Low-Voltage Rail-To-Rail Output Operational Amplifiers

Check for Samples: LMV321, LMV358, LMV324, LMV324S

FEATURES

- **2.7-V and 5-V Performance**
- **–40°C to 125°C Operation**
- **Low-Power Shutdown Mode (LMV324S)**
- **No Crossover Distortion**
- **Low Supply Current**
  - **LMV321 . . . 130 µA Typ**
  - **LMV358 . . . 210 µA Typ**
  - **LMV324 . . . 410 µA Typ**
  - **LMV324S . . . 410 µA Typ**
- **Rail-to-Rail Output Swing**
- **ESD Protection Exceeds JESD 22**
  - **2000-V Human-Body Model (A114-A)**
  - **1000-V Charged-Device Model (C101)**

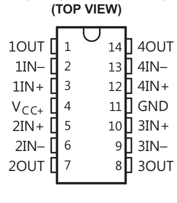
DESCRIPTION

The LMV321, LMV358, and LMV324/LMV324S are single, dual, and quad low-voltage (2.7 V to 5.5 V) operational amplifiers with rail-to-rail output swing. The LMV324S, which is a variation of the standard LMV324, includes a power-saving shutdown feature that reduces supply current to a maximum of 5 µA per channel when the amplifiers are not needed. Channels 1 and 2 together are put in shutdown, as are channels 3 and 4. While in shutdown, the outputs actively are pulled low.

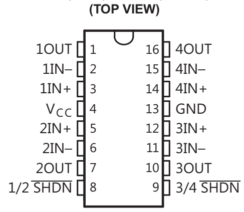
The LMV321, LMV358, LMV324, and LMV324S are the most cost-effective solutions for applications where low-voltage operation, space saving, and low cost are needed. These amplifiers are designed specifically for low-voltage (2.7 V to 5 V) operation, with performance specifications meeting or exceeding the LM358 and LM324 devices that operate from 5 V to 30 V. Additional features of the LMV3xx devices are a common-mode input voltage range that includes ground, 1-MHz unity-gain bandwidth, and 1-V/µs slew rate.

The LMV321 is available in the ultra-small DCK (SC-70) package, which is approximately one-half the size of the DBV (SOT-23) package. This package saves space on printed circuit boards and enables the design of small portable electronic devices. It also allows the designer to place the device closer to the signal source to reduce noise pickup and increase signal integrity.

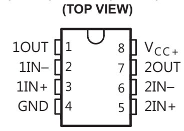
LMV324 . . . D (SOIC) OR PW (TSSOP) PACKAGE
(TOP VIEW)



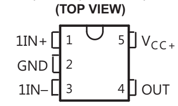
LMV324S . . . D (SOIC) OR PW (TSSOP) PACKAGE
(TOP VIEW)



LMV358 . . . D (SOIC), DDU (VSSOP),
DGK (MSOP), OR PW (TSSOP) PACKAGE
(TOP VIEW)

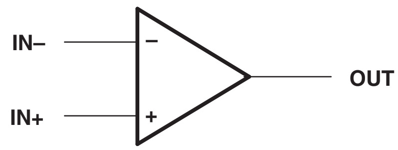


LMV321 . . . DBV (SOT-23) OR DCK (SC-70) PACKAGE
(TOP VIEW)

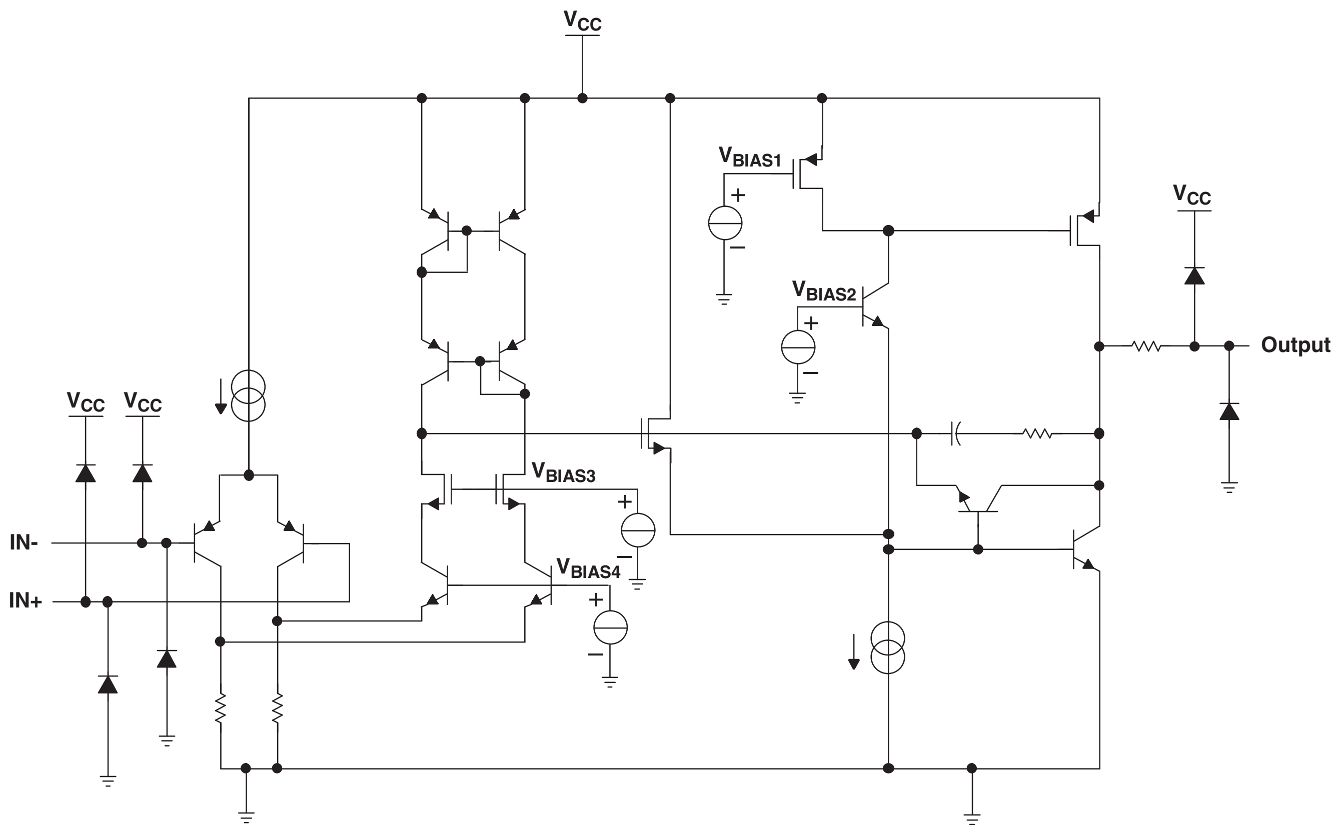


These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

Symbol (Each Amplifier)



LMV324 Simplified Schematic



Absolute Maximum Ratings[1]

over operating free-air temperature range (unless otherwise noted)

				MIN	MAX	UNIT
V_{CC}	Supply voltage[2]				5.5	V
V_{ID}	Differential input voltage[3]				±5.5	V
V_I	Input voltage range (either input)			–0.2	5.5	V
	Duration of output short circuit (one amplifier) to ground[4]	At or below T_A = 25°C, V_{CC} ≤ 5.5 V			Unlimited	
θ_{JA}	Package thermal impedance[5] [6]	D package	8 pin		97	°C/W
			14 pin		86	
			16 pin		73	
		DBV package	5 pin		206	
		DCK package	5 pin		252	
		DDU package	8 pin		210	
		DGK package	8 pin		172	
		PW package	8 pin		149	
			14 pin		113	
			16 pin		108	
T_J	Operating virtual junction temperature				150	°C
T_{stg}	Storage temperature range			–65	150	°C

(1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions* is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
(2) All voltage values (except differential voltages and V_{CC} specified for the measurement of I_{OS}) are with respect to the network GND.
(3) Differential voltages are at IN+ with respect to IN–.
(4) Short circuits from outputs to V_{CC} can cause excessive heating and eventual destruction.
(5) Maximum power dissipation is a function of T_J(max), θ_{JA}, and T_A. The maximum allowable power dissipation at any allowable ambient temperature is $P_D = (T_J(max) – T_A)/\theta_{JA}$. Operating at the absolute maximum T_J of 150°C can affect reliability.
(6) The package thermal impedance is calculated in accordance with JESD 51-7.

Recommended Operating Conditions[1]

			MIN	MAX	UNIT
V_{CC}	Supply voltage (single-supply operation)		2.7	5.5	V
V_{IH}	Amplifier turn-on voltage level (LMV324S)[2]	V_{CC} = 2.7 V	1.7		V
		V_{CC} = 5 V	3.5		
V_{IL}	Amplifier turn-off voltage level (LMV324S)	V_{CC} = 2.7 V		0.7	V
		V_{CC} = 5 V		1.5	
T_A	Operating free-air temperature	I temperature (LMV321, LMV358, LMV324, LMV321IDCK)	–40	125	°C
		I temperature (LMV324S)	-40	85	
		Q temperature	–40	125	

(1) All unused control inputs of the device must be held at V_{CC} or GND to ensure proper device operation. See the TI application report, *Implications of Slow or Floating CMOS Inputs*, literature number SCBA004.
(2) V_{IH} should not be allowed to exceed V_{CC}.

Electrical Characteristics

V_{CC+} = 2.7 V, T_A = 25°C (unless otherwise noted)

PARAMETER		TEST CONDITIONS		MIN	TYP[(1)]	MAX	UNIT
V_{IO}	Input offset voltage				1.7	7	mV
α_{VIO}	Average temperature coefficient of input offset voltage				5		µV/°C
I_{IB}	Input bias current				11	250	nA
I_{IO}	Input offset current				5	50	nA
CMRR	Common-mode rejection ratio	V_{CM} = 0 to 1.7 V		50	63		dB
k_{SVR}	Supply-voltage rejection ratio	V_{CC} = 2.7 V to 5 V, V_O = 1 V		50	60		dB
V_{ICR}	Common-mode input voltage range	CMRR ≥ 50 dB		0	–0.2		V
					1.9	1.7	
V_O	Output swing	R_L = 10 kΩ to 1.35 V	High level	V_{CC} – 100	V_{CC} – 10		mV
			Low level		60	180	
I_{CC}	Supply current	LMV321I			80	170	µA
		LMV358I (both amplifiers)			140	340	
		LMV324I/LMV324SI (all four amplifiers)			260	680	
B_1	Unity-gain bandwidth	C_L = 200 pF			1		MHz
Φ_m	Phase margin				60		deg
G_m	Gain margin				10		dB
V_n	Equivalent input noise voltage	f = 1 kHz			46		nV/√Hz
I_n	Equivalent input noise current	f = 1 kHz			0.17		pA/√Hz

(1) Typical values represent the likely parametric nominal values determined at the time of characterization. Typical values depend on the application and configuration and may vary over time. Typical values are not ensured on production material.

Shutdown Characteristics (LMV324S)

V_{CC+} = 2.7 V, T_A = 25°C (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP[(1)]	MAX	UNIT
$I_{CC(SHDN)}$	Supply current in shutdown mode (per channel)	$\overline{SHDN}$ ≤ 0.6 V			5	µA
$t_{(on)}$	Amplifier turn-on time	A_V = 1, R_L = Open (measured at 50% point)		2		µs
$t_{(off)}$	Amplifier turn-off time	A_V = 1, R_L = Open (measured at 50% point)		40		ns

(1) Typical values represent the likely parametric nominal values determined at the time of characterization. Typical values depend on the application and configuration and may vary over time. Typical values are not ensured on production material.

Electrical Characteristics

V_{CC+} = 5 V, at specified free-air temperature (unless otherwise noted)

PARAMETER		TEST CONDITIONS		T_A (1)	MIN	TYP (2)	MAX	UNIT
V_{IO}	Input offset voltage			25°C		1.7	7	mV
				Full range			9	
α_{VIO}	Average temperature coefficient of input offset voltage			25°C		5		μV/°C
I_{IB}	Input bias current			25°C		15	250	nA
				Full range			500	
I_{IO}	Input offset current			25°C		5	50	nA
				Full range			150	
CMRR	Common-mode rejection ratio	V_{CM} = 0 to 4 V		25°C	50	65		dB
k_{SVR}	Supply-voltage rejection ratio	V_{CC} = 2.7 V to 5 V, V_O = 1 V, V_{CM} = 1 V		25°C	50	60		dB
V_{ICR}	Common-mode input voltage range	CMRR ≥ 50 dB		25°C	0	–0.2		V
						4.2	4	
V_O	Output swing	R_L = 2 kΩ to 2.5 V	High level	25°C	V_{CC} – 300	V_{CC} – 40		mV
				Full range	V_{CC} – 400			
			Low level	25°C		120	300	
				Full range			400	
		R_L = 10 kΩ to 2.5 V	High level	25°C	V_{CC} – 100	V_{CC} – 10		
				Full range	V_{CC} – 200			
			Low level	25°C		65	180	
				Full range			280	
A_{VD}	Large-signal differential voltage gain	R_L = 2 kΩ		25°C	15	100		V/mV
				Full range	10			
I_{OS}	Output short-circuit current	Sourcing, V_O = 0 V		25°C	5	60		mA
		Sinking, V_O = 5 V			10	160		
I_{CC}	Supply current	LMV321I		25°C		130	250	μA
				Full range			350	
		LMV358I (both amplifiers)		25°C		210	440	
				Full range			615	
		LMV324I/LMV324SI (all four amplifiers)		25°C		410	830	
				Full range			1160	
B_1	Unity-gain bandwidth	C_L = 200 pF		25°C		1		MHz
Φ_m	Phase margin			25°C		60		deg
G_m	Gain margin			25°C		10		dB
V_n	Equivalent input noise voltage	f = 1 kHz		25°C		39		nV/√Hz
I_n	Equivalent input noise current	f = 1 kHz		25°C		0.21		pA/√Hz
SR	Slew rate			25°C		1		V/μs

(1) Full range T_A = –40°C to 125°C for I temperature(LMV321, LMV358, LMV324, LMV321IDCK), –40°C to 85°C for (LMV324S) and –40°C to 125°C for Q temperature.
(2) Typical values represent the likely parametric nominal values determined at the time of characterization. Typical values depend on the application and configuration and may vary over time. Typical values are not ensured on production material.

Shutdown Characteristics (LMV324S)

V_{CC+} = 5 V, T_A = 25°C (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP(1)	MAX	UNIT
$I_{CC(SHDN)}$	Supply current in shutdown mode (per channel)	$\overline{SHDN}$ ≤ 0.6 V, T_A = Full Temperature Range			5	μA
$t_{(on)}$	Amplifier turn-on time	A_V = 1, R_L = Open (measured at 50% point)		2		μs
$t_{(off)}$	Amplifier turn-off time	A_V = 1, R_L = Open (measured at 50% point)		40		ns

(1) Typical values represent the likely parametric nominal values determined at the time of characterization. Typical values depend on the application and configuration and may vary over time. Typical values are not ensured on production material.

Typical Characteristics

LMV321 FREQUENCY RESPONSE
vs
RESISTIVE LOAD

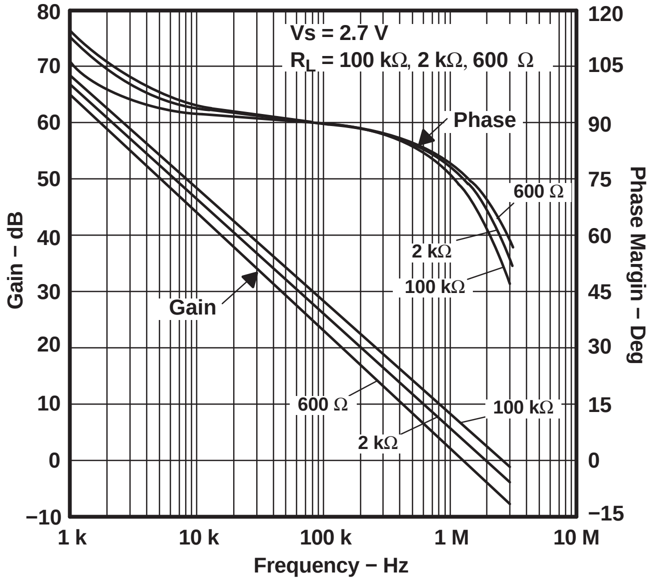


Figure 1.

LMV321 FREQUENCY RESPONSE
vs
RESISTIVE LOAD

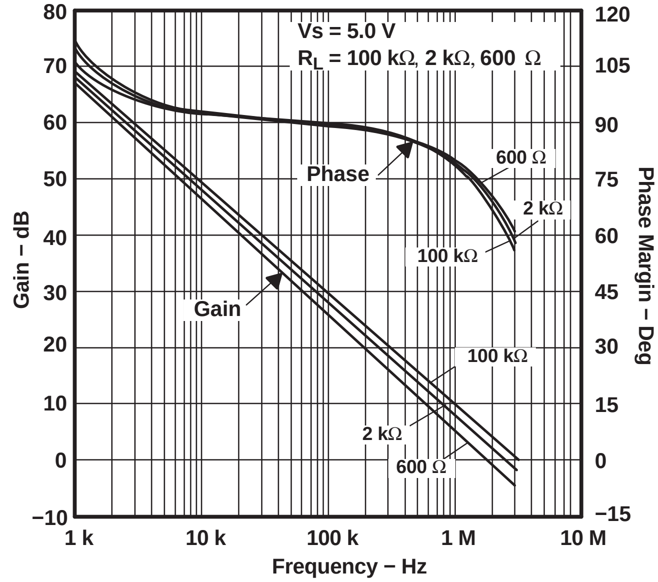


Figure 2.

LMV321 FREQUENCY RESPONSE
vs
CAPACITIVE LOAD

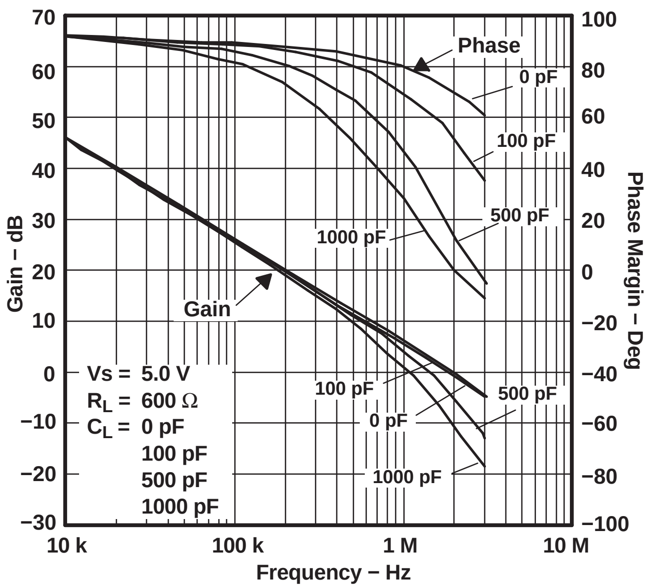


Figure 3.

LMV321 FREQUENCY RESPONSE
vs
CAPACITIVE LOAD

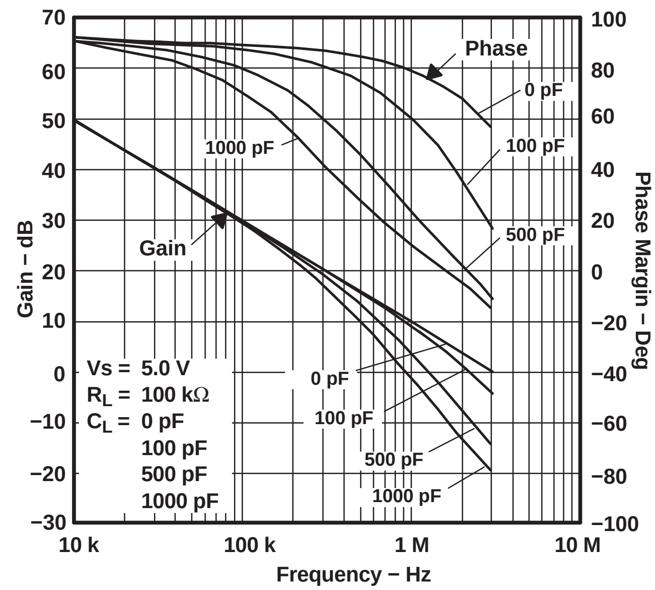


Figure 4.

Typical Characteristics (continued)

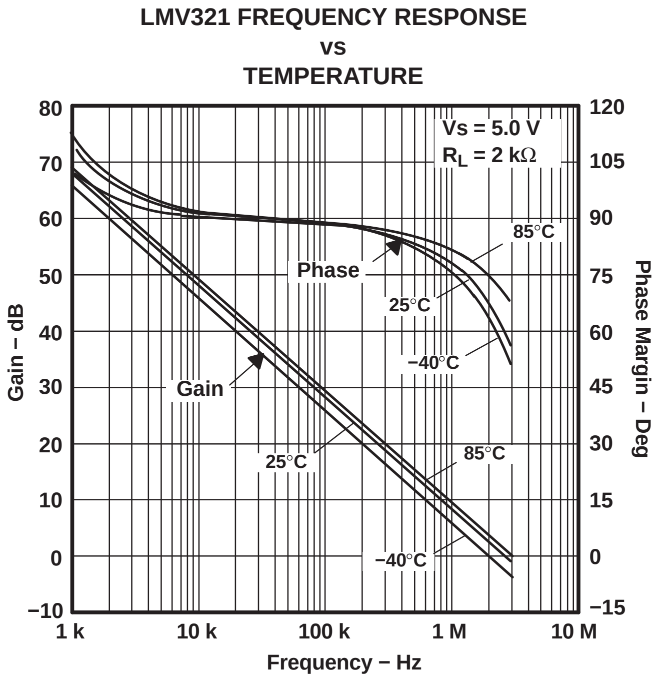


Figure 5.

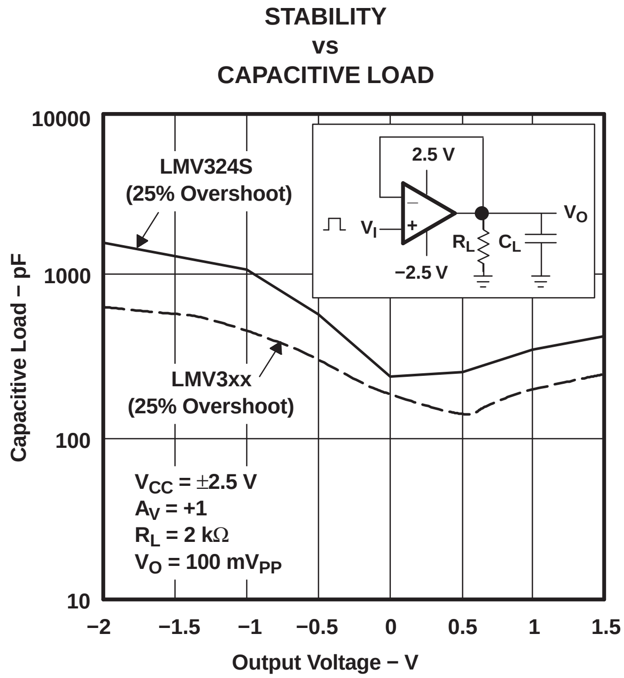
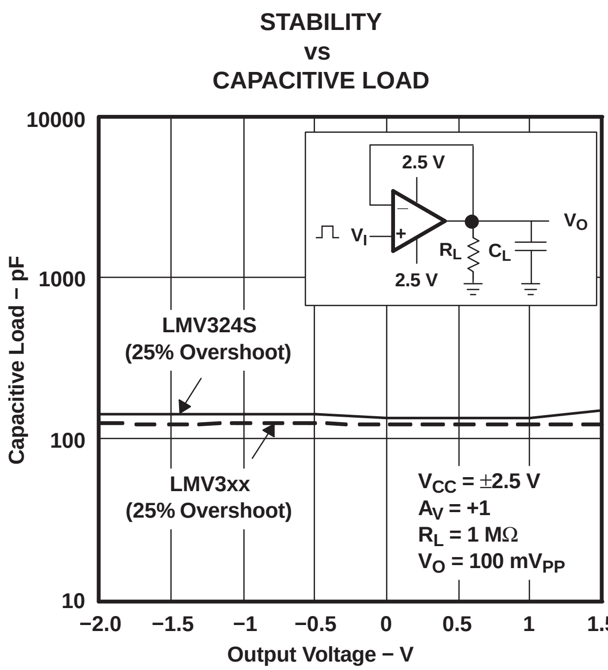


Figure 6.



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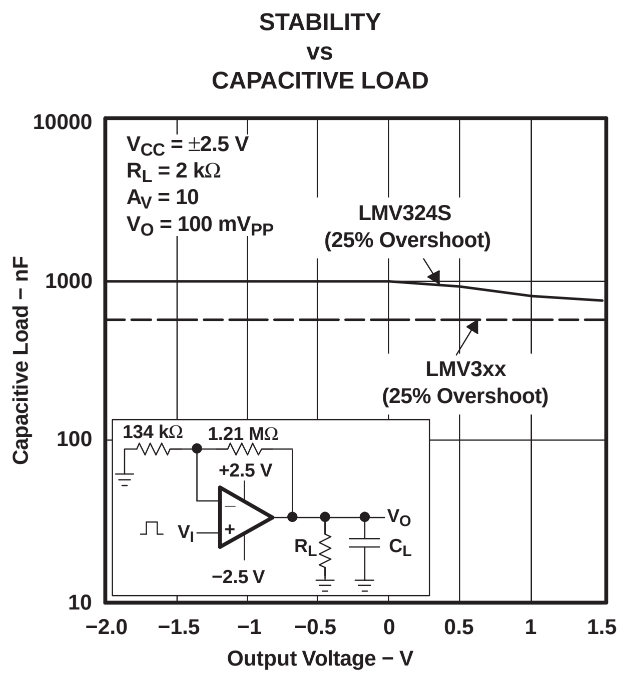
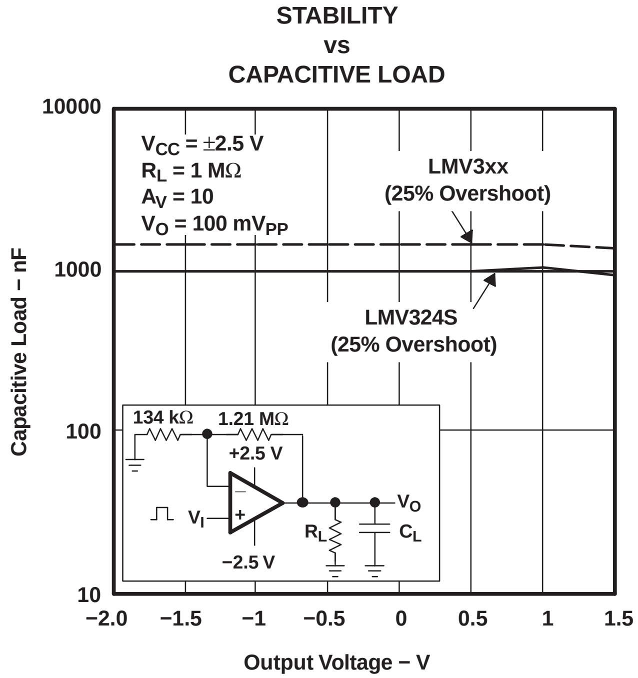


Figure 8.

Typical Characteristics (continued)



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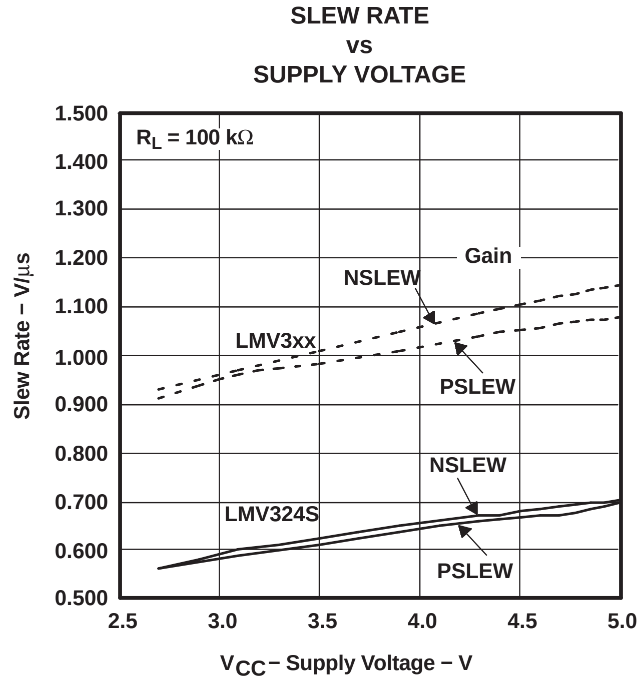

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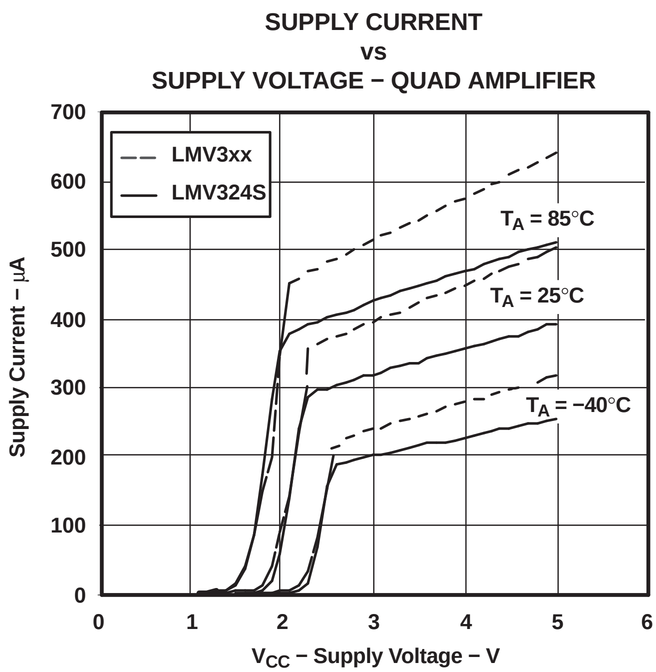

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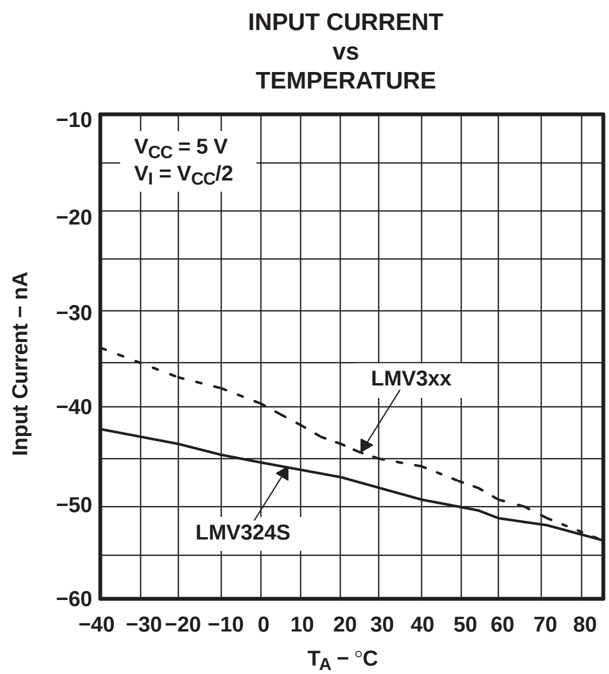


Figure 12.

Typical Characteristics (continued)

SOURCE CURRENT
vs
OUTPUT VOLTAGE

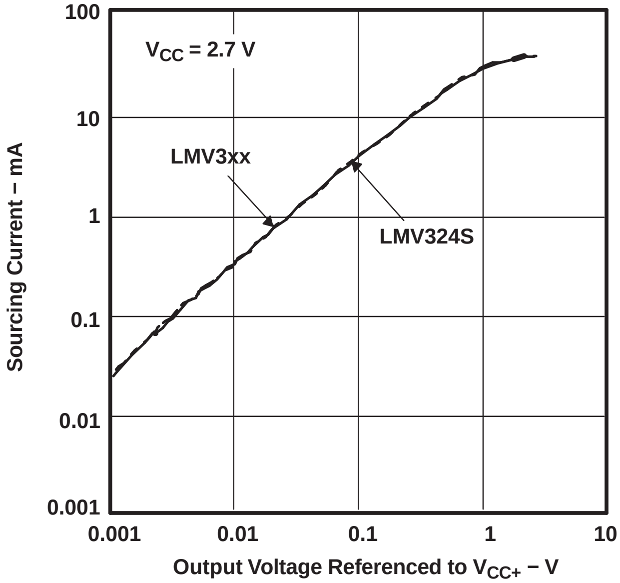


Figure 13.

SOURCE CURRENT
vs
OUTPUT VOLTAGE

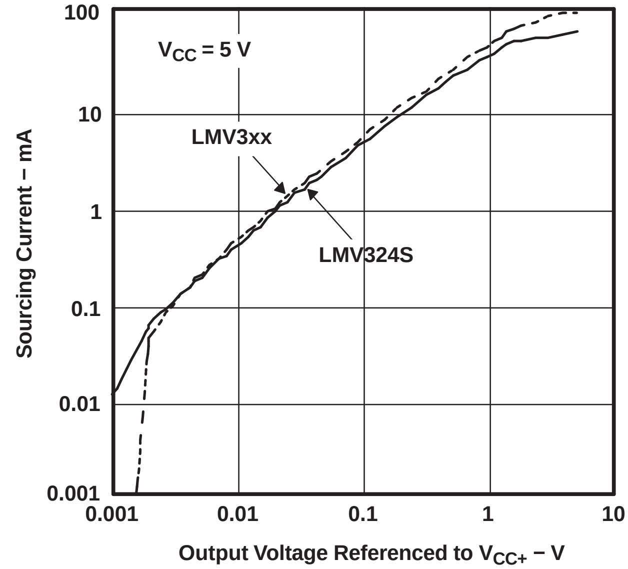


Figure 14.

SINKING CURRENT
vs
OUTPUT VOLTAGE

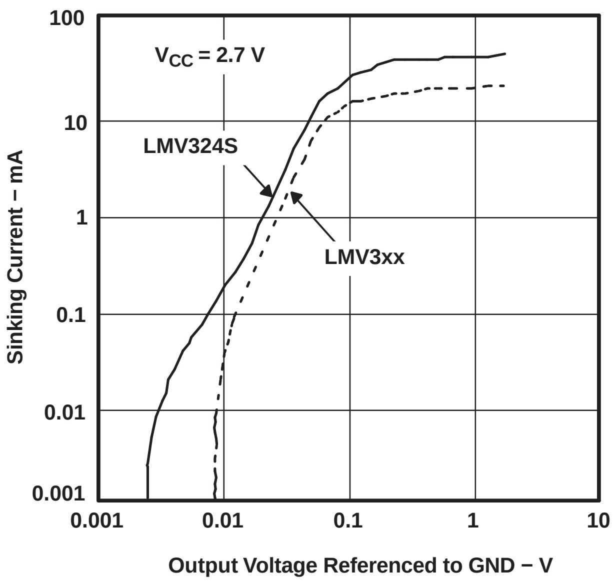


Figure 15.

SINKING CURRENT
vs
OUTPUT VOLTAGE

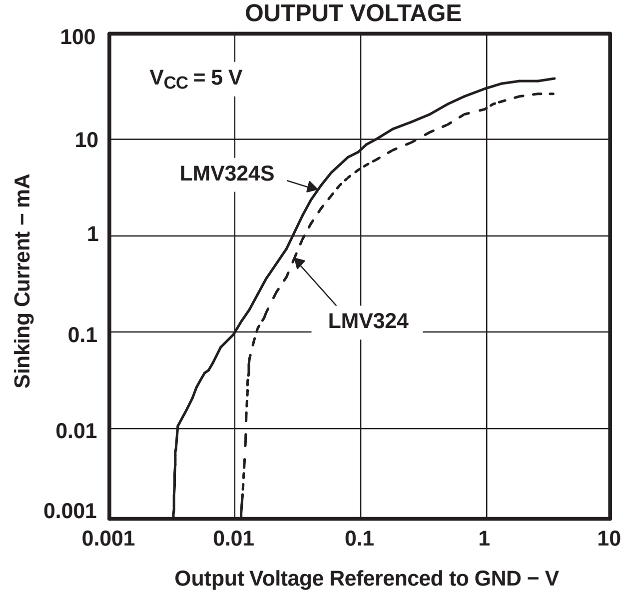


Figure 16.

Typical Characteristics (continued)

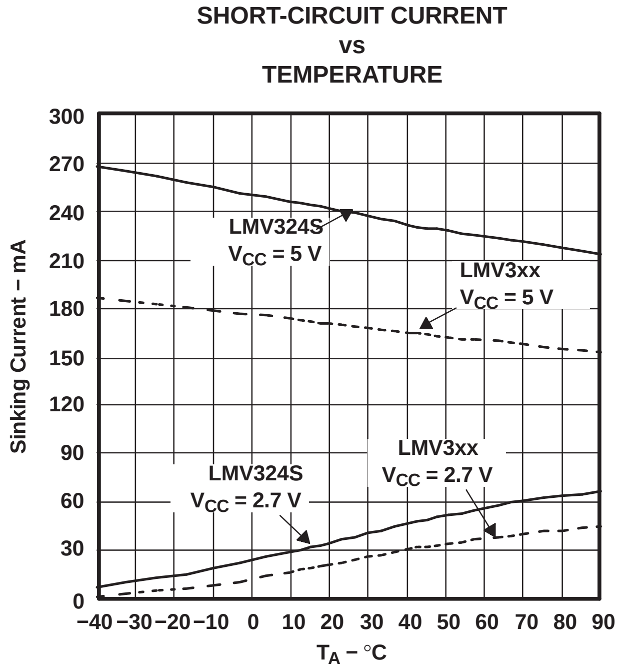
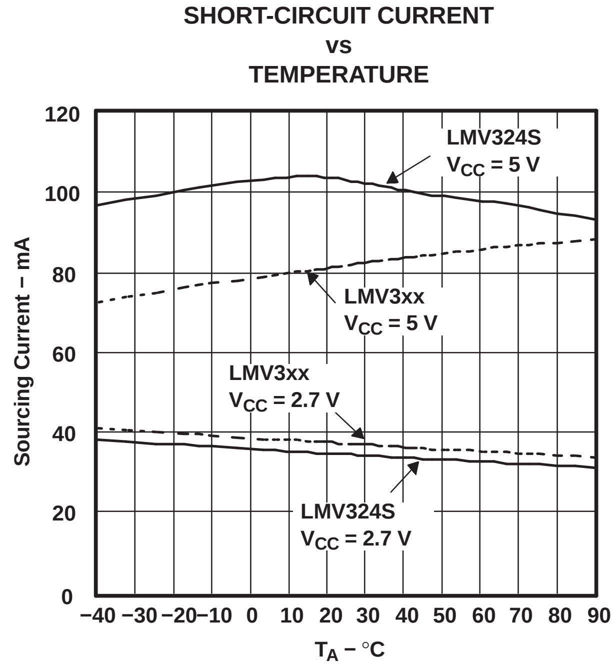


Figure 17.



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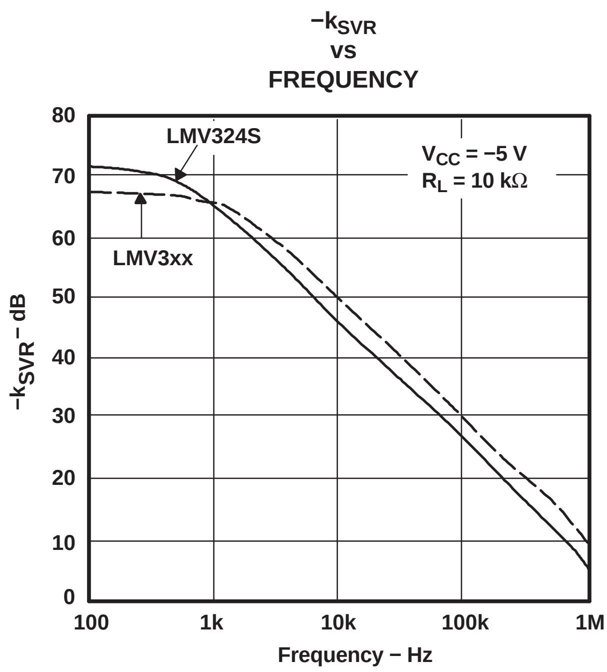

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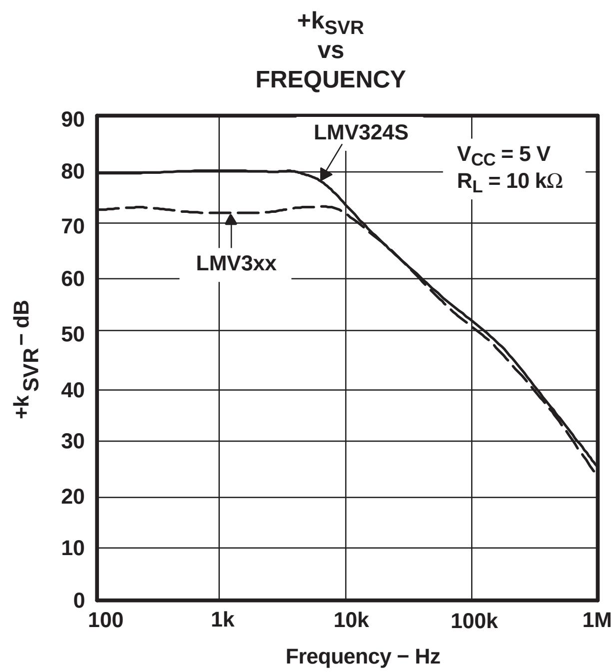


Figure 20.

Typical Characteristics (continued)

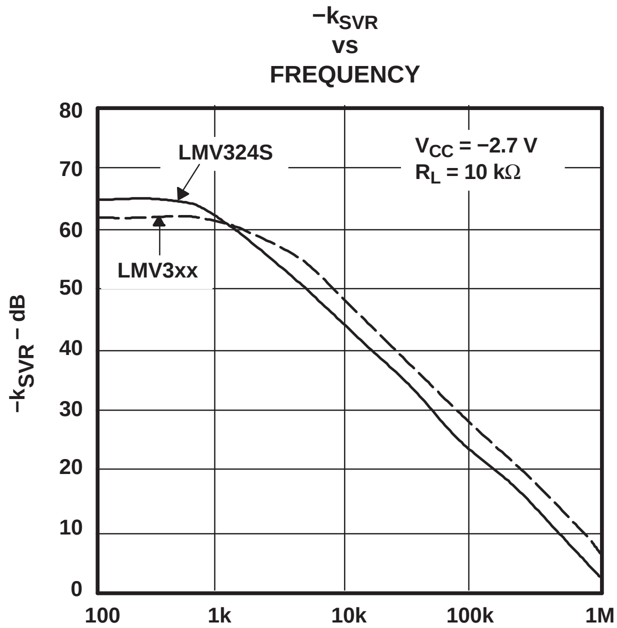


Figure 21.

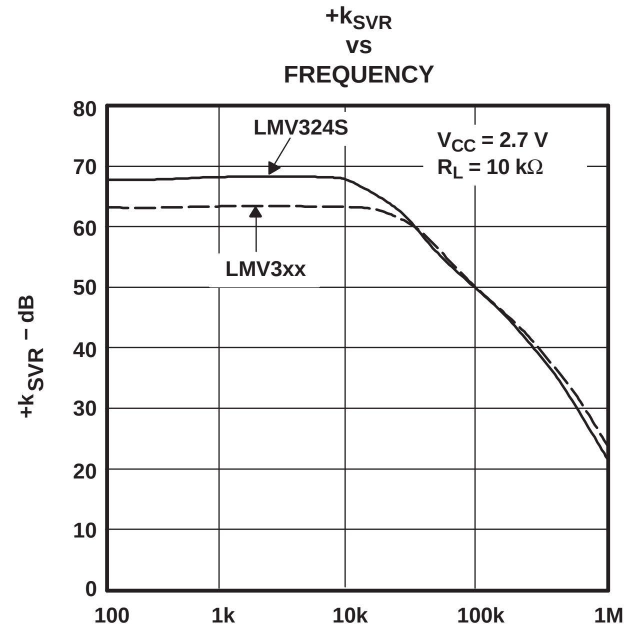


Figure 22.

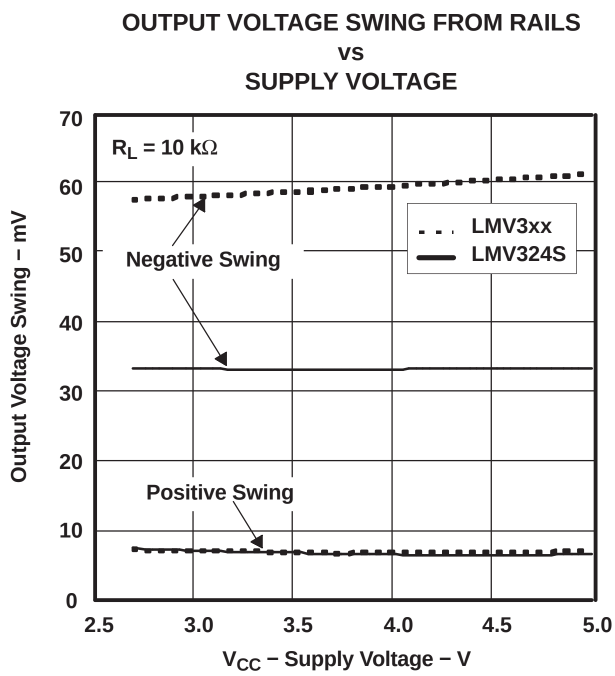


Figure 23.

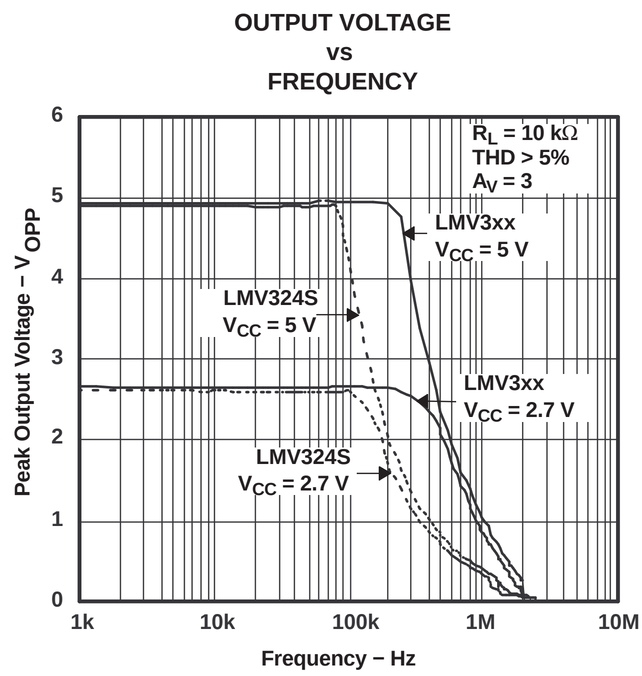


Figure 24.

Typical Characteristics (continued)

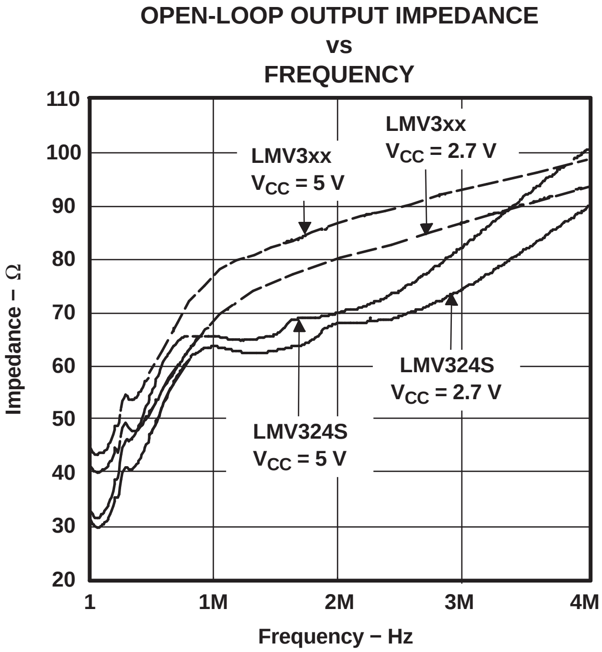


Figure 25.

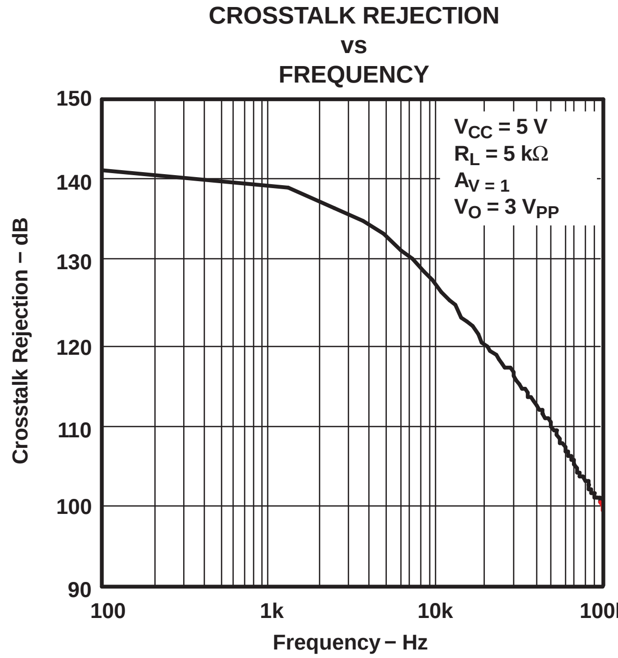
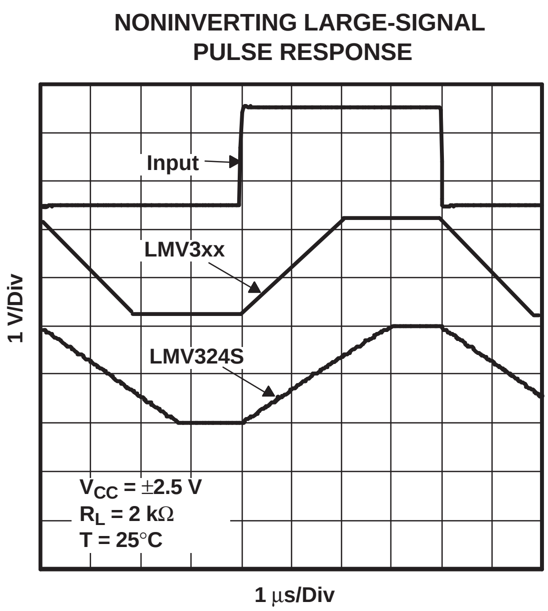


Figure 26.



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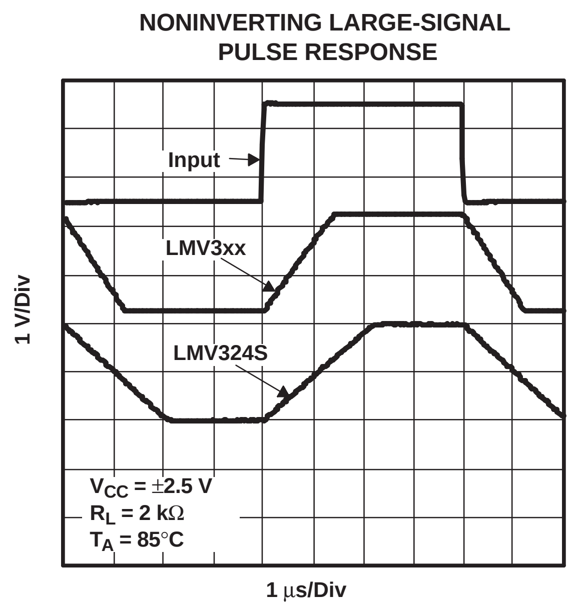

Figure 28.

Typical Characteristics (continued)

NONINVERTING LARGE-SIGNAL PULSE RESPONSE

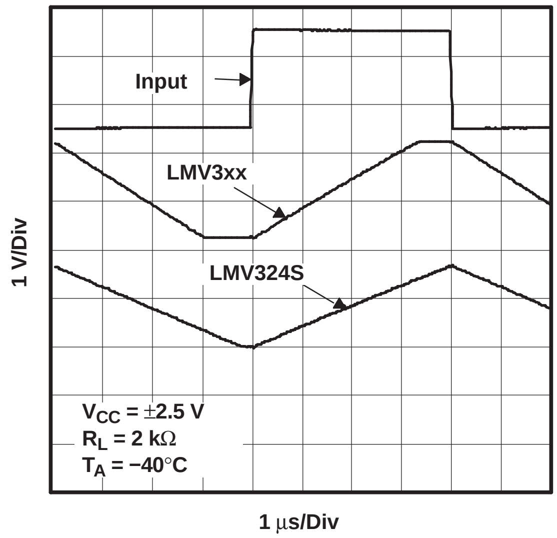

Figure 29.

NONINVERTING SMALL-SIGNAL PULSE RESPONSE

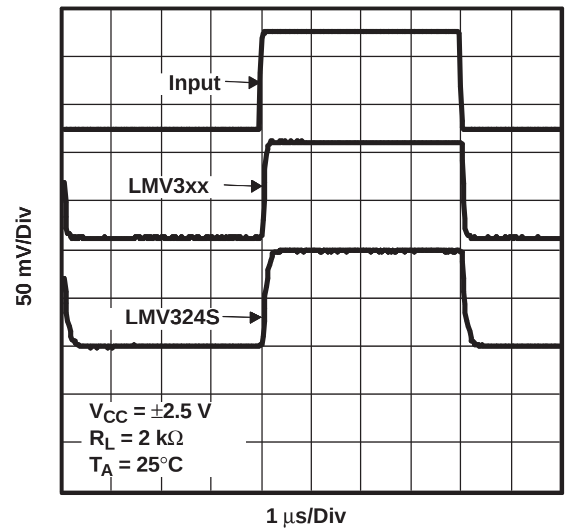

Figure 30.

NONINVERTING SMALL-SIGNAL PULSE RESPONSE

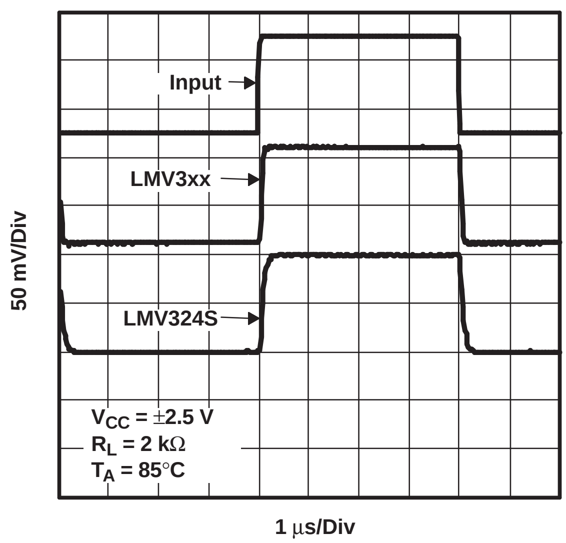

Figure 31.

NONINVERTING SMALL-SIGNAL PULSE RESPONSE

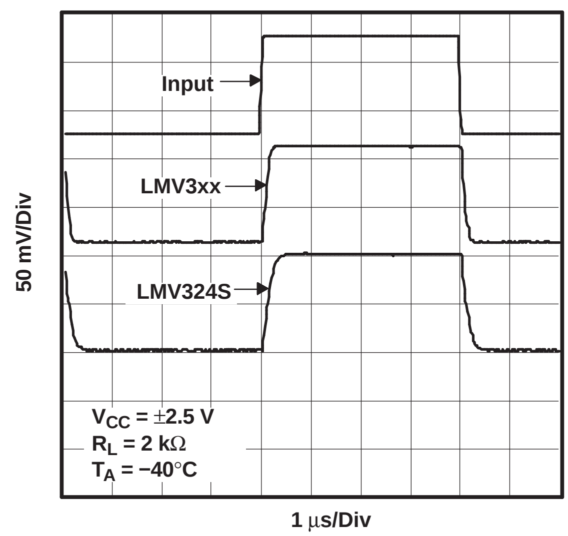

Figure 32.

Typical Characteristics (continued)

INVERTING LARGE-SIGNAL PULSE RESPONSE

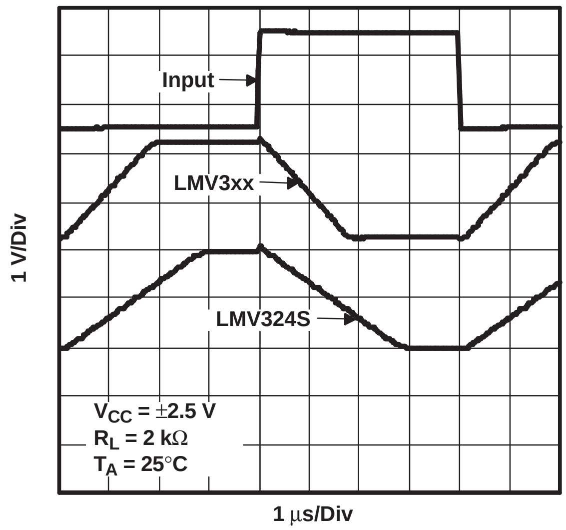

Figure 33.

INVERTING LARGE-SIGNAL PULSE RESPONSE

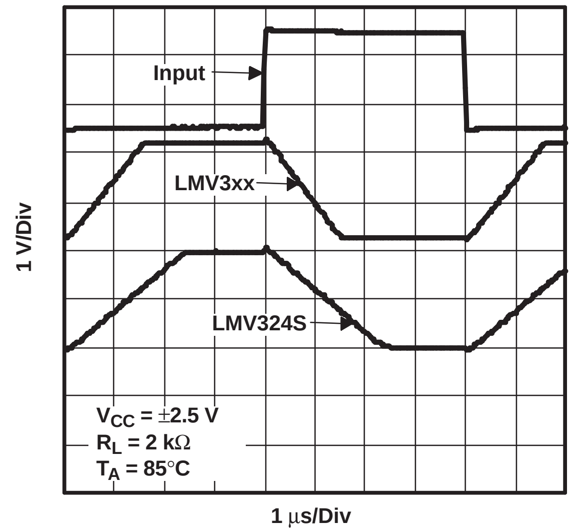

Figure 34.

INVERTING LARGE-SIGNAL PULSE RESPONSE

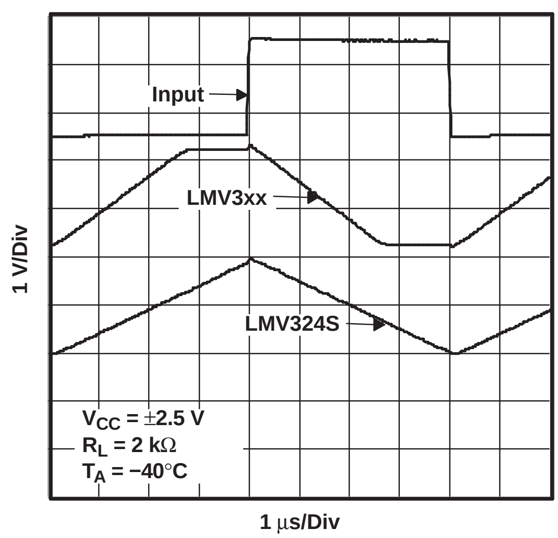

Figure 35.

INVERTING SMALL-SIGNAL PULSE RESPONSE

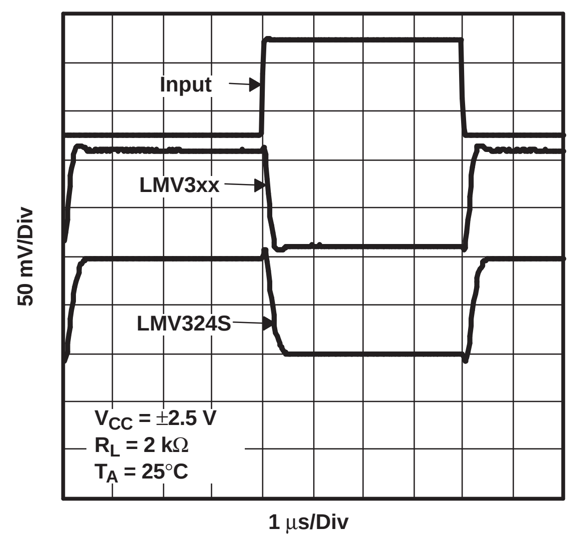

Figure 36.

Typical Characteristics (continued)

INVERTING SMALL-SIGNAL
PULSE RESPONSE

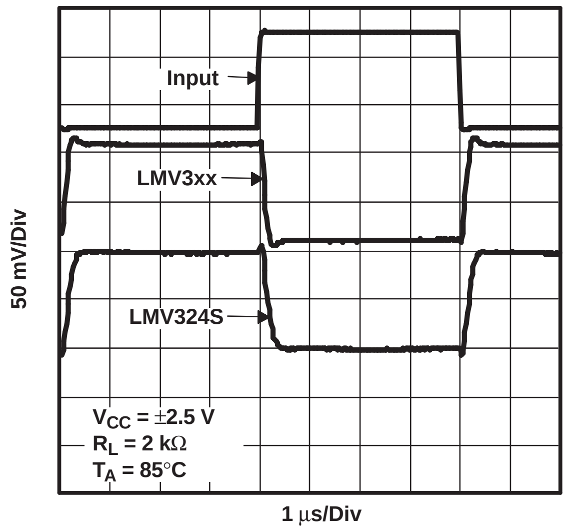

Figure 37.

INVERTING SMALL-SIGNAL
PULSE RESPONSE

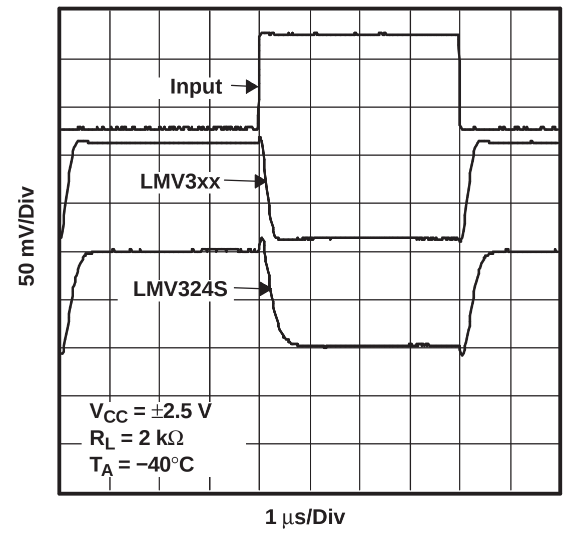

Figure 38.

INPUT CURRENT NOISE
vs
FREQUENCY

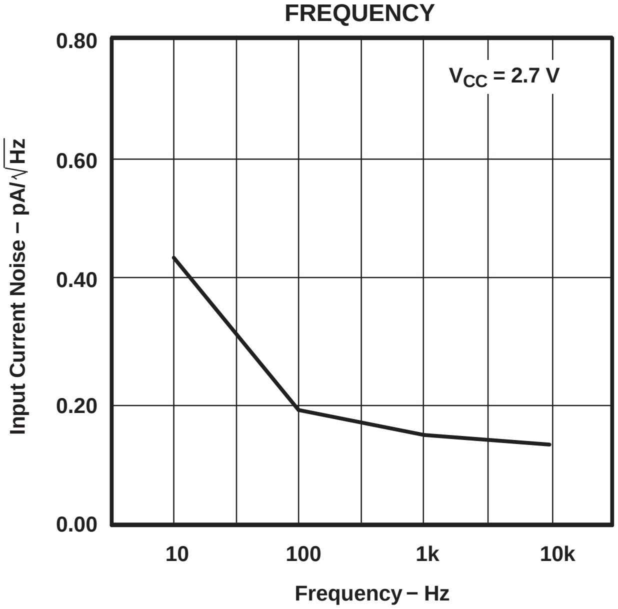

Figure 39.

INPUT CURRENT NOISE
vs
FREQUENCY

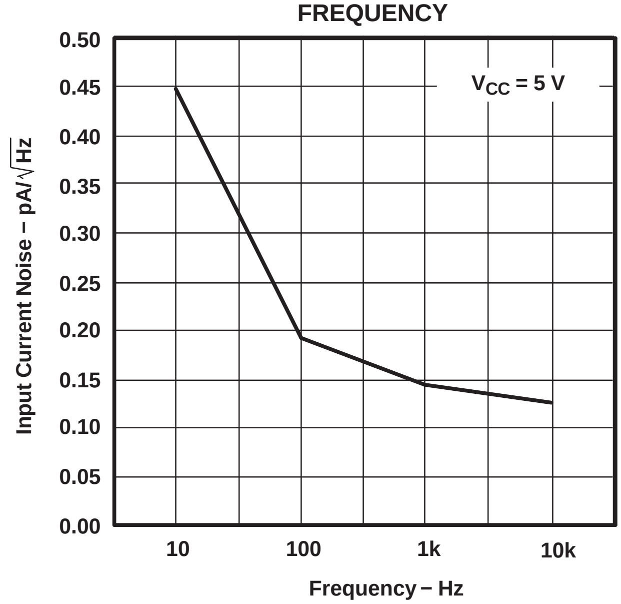

Figure 40.

Typical Characteristics (continued)

INPUT VOLTAGE NOISE vs FREQUENCY

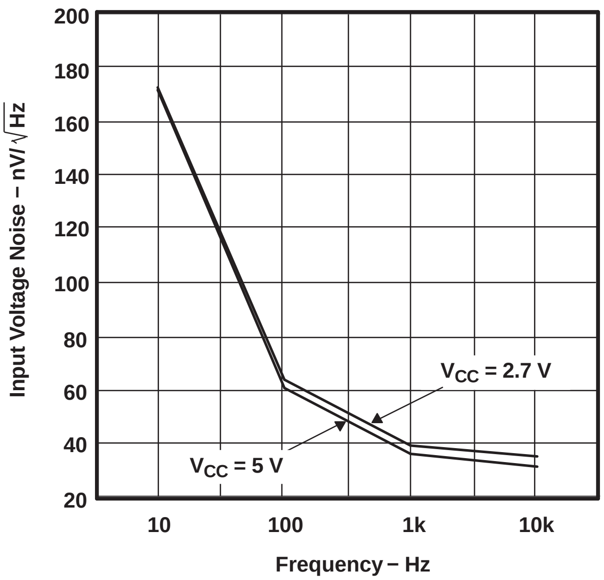

Figure 41.

THD + N vs FREQUENCY

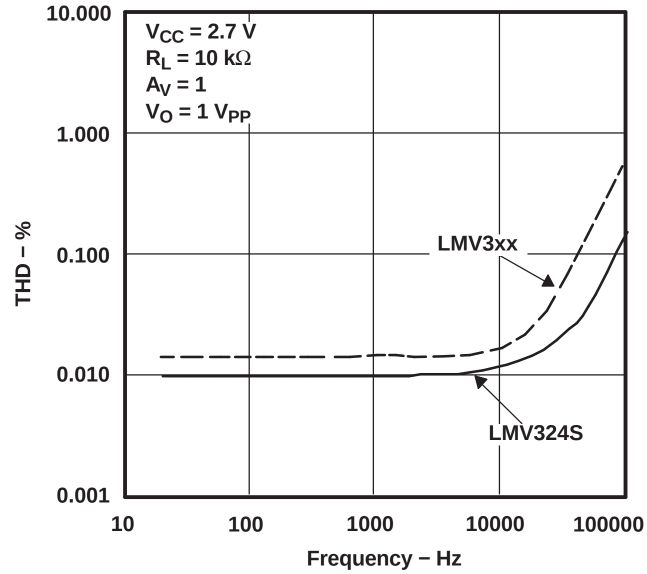

Figure 42.

THD + N vs FREQUENCY

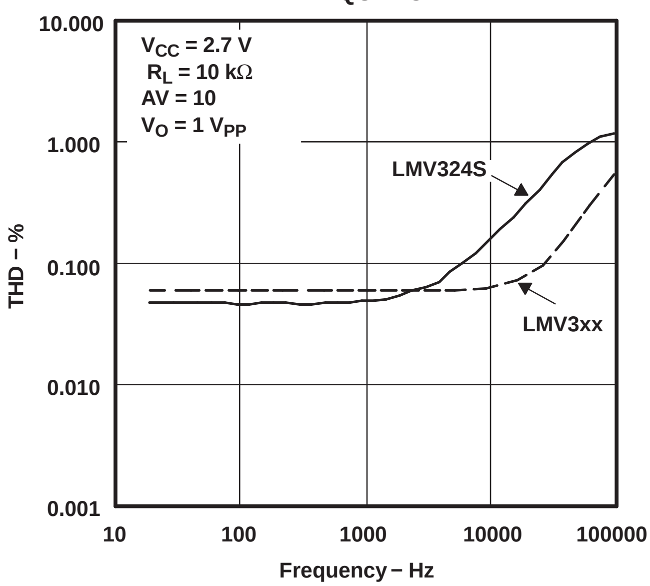

Figure 43.

THD + N vs FREQUENCY

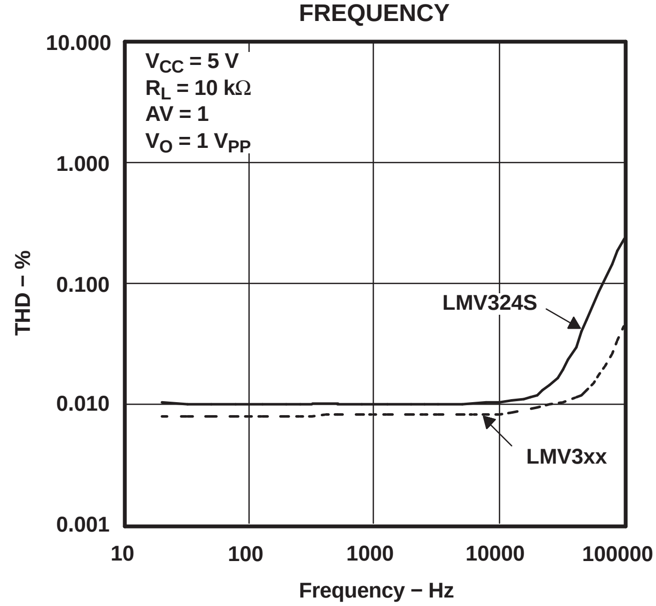

Figure 44.

Typical Characteristics (continued)

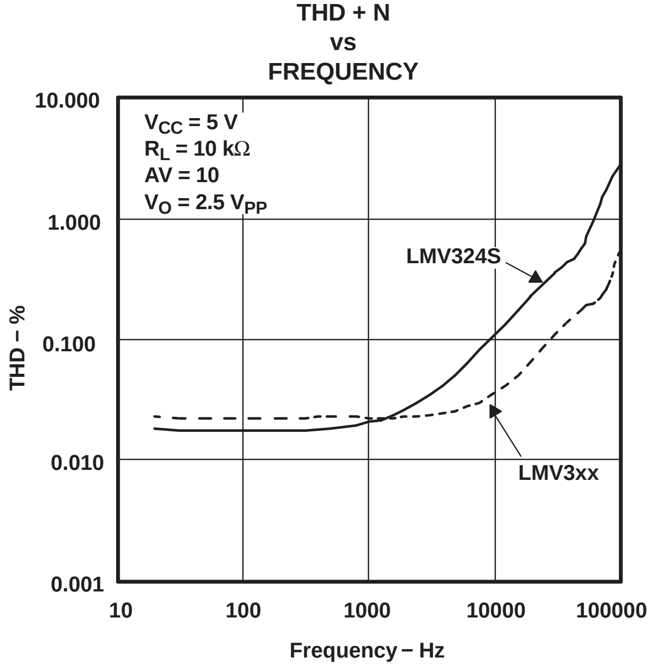

Figure 45.

REVISION HISTORY

Changes from Revision T (September 2007) to Revision U	Page
• Updated $θ_{JA}$ value for DDU package.	3

Changes from Revision U (July 2012) to Revision V	Page
• Updated document to new TI data sheet format.	1
• Added ESD warning.	2
• Removed Ordering Information table.	2
• Updated operating temperature range for LMV321IDCK.	3

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
LMV321IDBVR	ACTIVE	SOT-23	DBV	5	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	(RC1F ~ RC1K)	Samples
LMV321IDBVRG4	ACTIVE	SOT-23	DBV	5	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	(RC1F ~ RC1K)	Samples
LMV321IDBVT	ACTIVE	SOT-23	DBV	5	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	(RC1F ~ RC1K)	Samples
LMV321IDBVTE4	ACTIVE	SOT-23	DBV	5	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	(RC1F ~ RC1K)	Samples
LMV321IDBVTG4	ACTIVE	SOT-23	DBV	5	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	(RC1F ~ RC1K)	Samples
LMV321IDCKR	ACTIVE	SC70	DCK	5	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	(R3C ~ R3I ~ R3O ~ R3R ~ R3Z)	Samples
LMV321IDCKRG4	ACTIVE	SC70	DCK	5	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	(R3C ~ R3I ~ R3O ~ R3R ~ R3Z)	Samples
LMV321IDCKT	ACTIVE	SC70	DCK	5	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	(R3C ~ R3I ~ R3R)	Samples
LMV321IDCKTG4	ACTIVE	SC70	DCK	5	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	(R3C ~ R3I ~ R3R)	Samples
LMV324ID	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	LMV324I	Samples
LMV324IDG4	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	LMV324I	Samples
LMV324IDR	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU NIPDAU | CU SN	Level-1-260C-UNLIM	-40 to 125	LMV324I	Samples
LMV324IDRG4	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	LMV324I	Samples
LMV324IPWR	ACTIVE	TSSOP	PW	14	2000	Green (RoHS & no Sb/Br)	CU NIPDAU | CU SN	Level-1-260C-UNLIM	-40 to 125	MV324I	Samples
LMV324IPWRG4	ACTIVE	TSSOP	PW	14	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	MV324I	Samples
LMV324QD	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	LMV324Q	Samples
LMV324QDG4	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	LMV324Q	Samples

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
LMV324QDR	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	LMV324Q	Samples
LMV324QDRG4	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	LMV324Q	Samples
LMV324QPW	ACTIVE	TSSOP	PW	14	90	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	MV324Q	Samples
LMV324QPWG4	ACTIVE	TSSOP	PW	14	90	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	MV324Q	Samples
LMV324QPWR	ACTIVE	TSSOP	PW	14	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	MV324Q	Samples
LMV324SID	OBSOLETE	SOIC	D	16		TBD	Call TI	Call TI	-40 to 85	LMV324SI	
LMV324SIDE4	OBSOLETE	SOIC	D	16		TBD	Call TI	Call TI	-40 to 85		
LMV324SIDG4	OBSOLETE	SOIC	D	16		TBD	Call TI	Call TI	-40 to 85		
LMV324SIDR	OBSOLETE	SOIC	D	16		TBD	Call TI	Call TI	-40 to 85	LMV324SI	
LMV324SIDRE4	OBSOLETE	SOIC	D	16		TBD	Call TI	Call TI	-40 to 85		
LMV324SIDRG4	OBSOLETE	SOIC	D	16		TBD	Call TI	Call TI	-40 to 85		
LMV324SIPWR	OBSOLETE	TSSOP	PW	16		TBD	Call TI	Call TI	-40 to 85	MV324SI	
LMV324SIPWRE4	OBSOLETE	TSSOP	PW	16		TBD	Call TI	Call TI	-40 to 85		
LMV324SIPWRG4	OBSOLETE	TSSOP	PW	16		TBD	Call TI	Call TI	-40 to 85		
LMV358ID	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	MV358I	Samples
LMV358IDDUR	ACTIVE	VSSOP	DDU	8	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	RA5R	Samples
LMV358IDDURG4	ACTIVE	VSSOP	DDU	8	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	RA5R	Samples
LMV358IDE4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	MV358I	Samples
LMV358IDG4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	MV358I	Samples
LMV358IDGKR	ACTIVE	VSSOP	DGK	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	(R5B ~ R5Q ~ R5R)	Samples
LMV358IDGKRG4	ACTIVE	VSSOP	DGK	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	(R5B ~ R5Q ~ R5R)	Samples
LMV358IDR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU | CU SN	Level-1-260C-UNLIM	-40 to 125	MV358I	Samples

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
LMV358IDRE4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	MV358I	Samples
LMV358IDRG4	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	MV358I	Samples
LMV358IPW	ACTIVE	TSSOP	PW	8	150	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	MV358I	Samples
LMV358IPWG4	ACTIVE	TSSOP	PW	8	150	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	MV358I	Samples
LMV358IPWR	ACTIVE	TSSOP	PW	8	2000	Green (RoHS & no Sb/Br)	CU NIPDAU | CU SN	Level-1-260C-UNLIM	-40 to 125	MV358I	Samples
LMV358IPWRE4	ACTIVE	TSSOP	PW	8	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	MV358I	Samples
LMV358IPWRG4	ACTIVE	TSSOP	PW	8	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	MV358I	Samples
LMV358QD	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	MV358Q	Samples
LMV358QDDUR	ACTIVE	VSSOP	DDU	8	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	RAHR	Samples
LMV358QDDURG4	ACTIVE	VSSOP	DDU	8	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	RAHR	Samples
LMV358QDG4	ACTIVE	SOIC	D	8	75	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	MV358Q	Samples
LMV358QDGKR	ACTIVE	VSSOP	DGK	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	(RHO ~ RHR)	Samples
LMV358QDGKRG4	ACTIVE	VSSOP	DGK	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	(RHO ~ RHR)	Samples
LMV358QDR	ACTIVE	SOIC	D	8	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	MV358Q	Samples
LMV358QPWR	ACTIVE	TSSOP	PW	8	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 125	MV358Q	Samples

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.
TBD: The Pb-Free/Green conversion plan has not been defined.
Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.
Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.
Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

OTHER QUALIFIED VERSIONS OF LMV324, LMV358 :

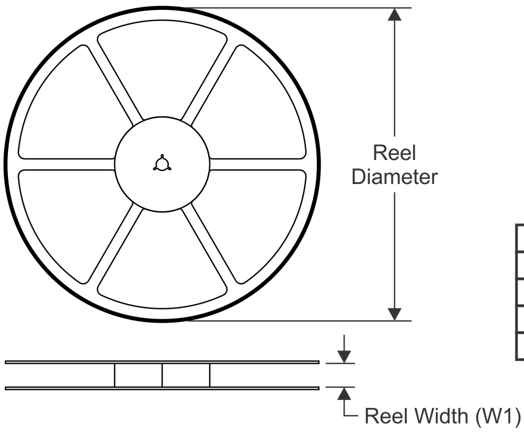
- Automotive: LMV324-Q1, LMV358-Q1

NOTE: Qualified Version Definitions:

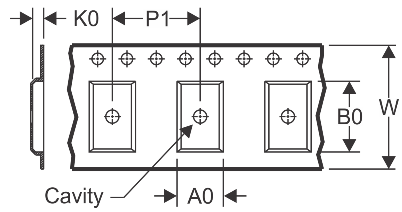
- Automotive - Q100 devices qualified for high-reliability automotive applications targeting zero defects

TAPE AND REEL INFORMATION

REEL DIMENSIONS

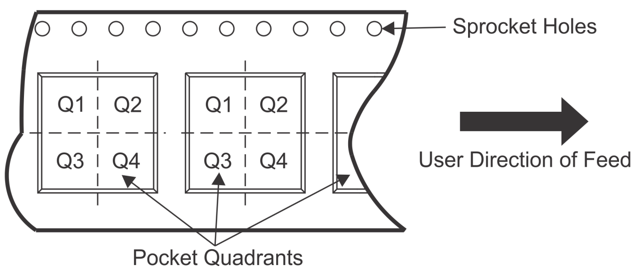


TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE

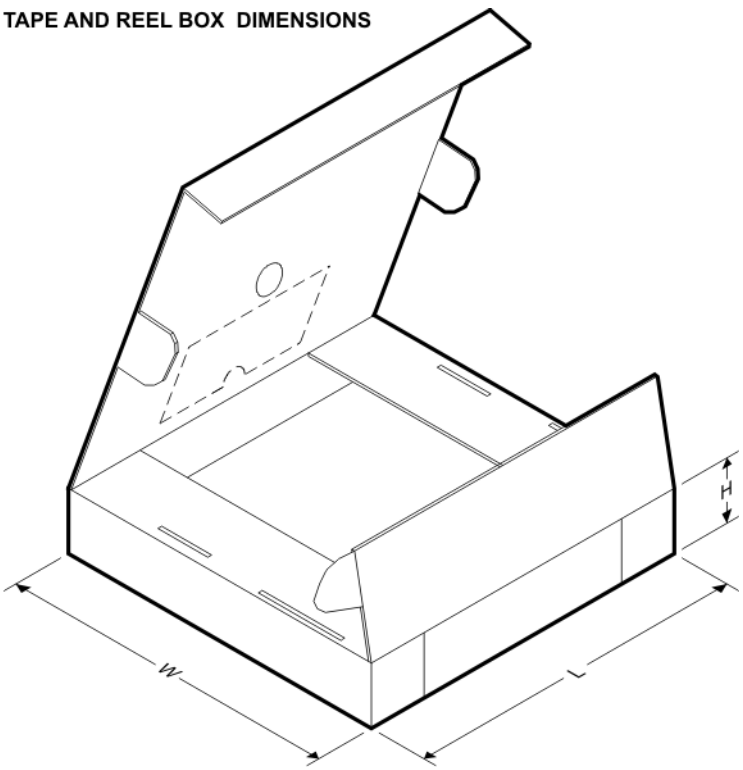


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
LMV321IDBVR	SOT-23	DBV	5	3000	178.0	9.0	3.23	3.17	1.37	4.0	8.0	Q3
LMV321IDBVR	SOT-23	DBV	5	3000	180.0	9.2	3.17	3.23	1.37	4.0	8.0	Q3
LMV321IDBVT	SOT-23	DBV	5	250	180.0	9.2	3.17	3.23	1.37	4.0	8.0	Q3
LMV321IDBVT	SOT-23	DBV	5	250	178.0	9.0	3.23	3.17	1.37	4.0	8.0	Q3
LMV321IDCKR	SC70	DCK	5	3000	178.0	9.0	2.4	2.5	1.2	4.0	8.0	Q3
LMV321IDCKR	SC70	DCK	5	3000	180.0	9.2	2.3	2.55	1.2	4.0	8.0	Q3
LMV321IDCKT	SC70	DCK	5	250	180.0	9.2	2.3	2.55	1.2	4.0	8.0	Q3
LMV321IDCKT	SC70	DCK	5	250	178.0	9.0	2.4	2.5	1.2	4.0	8.0	Q3
LMV324IDR	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
LMV324IDR	SOIC	D	14	2500	330.0	16.8	6.5	9.5	2.3	8.0	16.0	Q1
LMV324IDRG4	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
LMV324IPWR	TSSOP	PW	14	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
LMV324IPWRG4	TSSOP	PW	14	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
LMV324QDR	SOIC	D	14	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
LMV324QPWR	TSSOP	PW	14	2000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1
LMV358IDDUR	VSSOP	DDU	8	3000	180.0	8.4	2.25	3.35	1.05	4.0	8.0	Q3
LMV358IDGKR	VSSOP	DGK	8	2500	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1
LMV358IDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
LMV358IDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
LMV358IDR	SOIC	D	8	2500	330.0	12.8	6.4	5.2	2.1	8.0	12.0	Q1
LMV358IDRG4	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
LMV358IPWR	TSSOP	PW	8	2000	330.0	12.4	7.0	3.6	1.6	8.0	12.0	Q1
LMV358QDDUR	VSSOP	DDU	8	3000	180.0	8.4	2.25	3.35	1.05	4.0	8.0	Q3
LMV358QDGKR	VSSOP	DGK	8	2500	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1
LMV358QDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1

TAPE AND REEL BOX DIMENSIONS

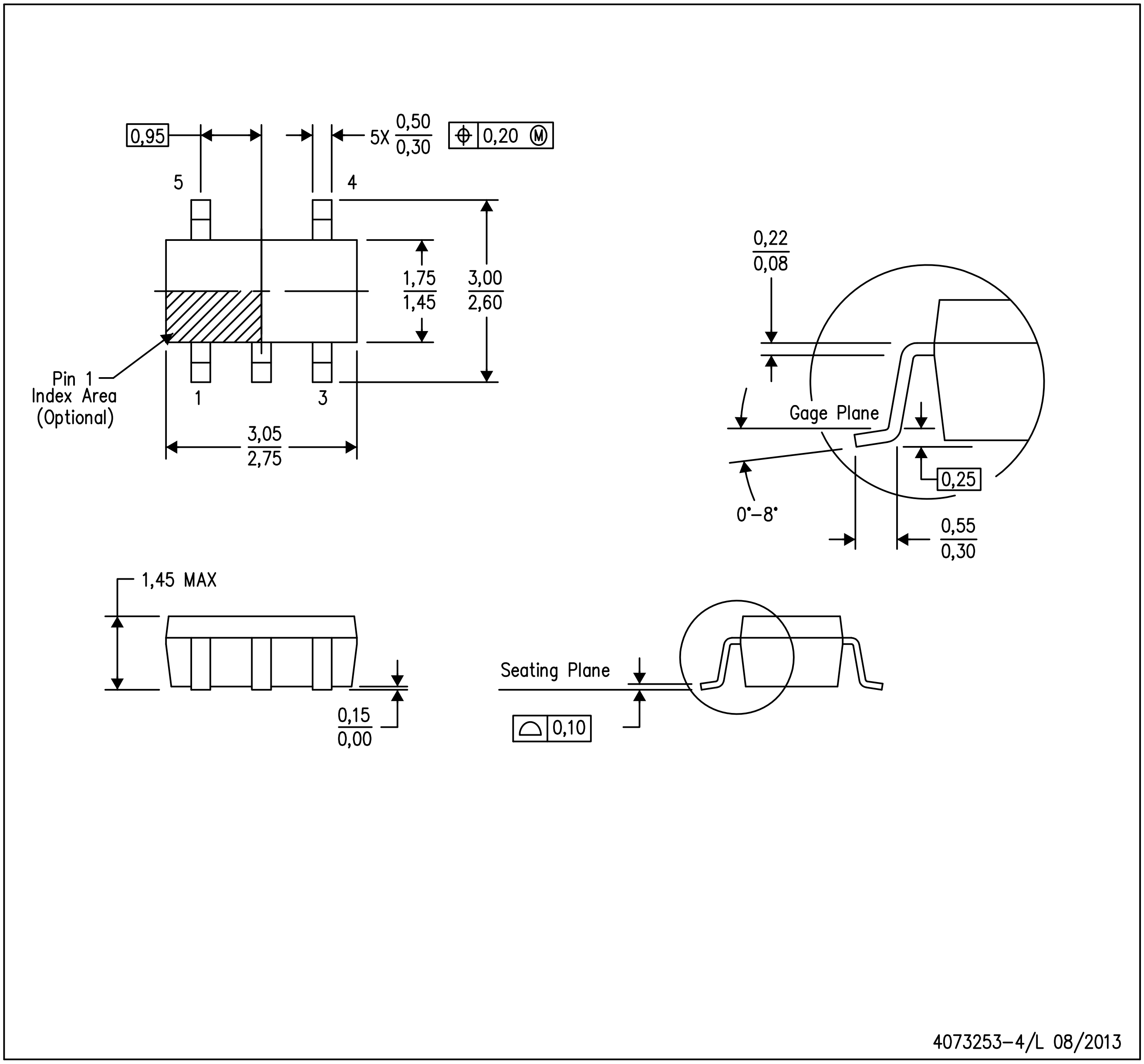


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
LMV321IDBVR	SOT-23	DBV	5	3000	180.0	180.0	18.0
LMV321IDBVR	SOT-23	DBV	5	3000	205.0	200.0	33.0
LMV321IDBVT	SOT-23	DBV	5	250	205.0	200.0	33.0
LMV321IDBVT	SOT-23	DBV	5	250	180.0	180.0	18.0
LMV321IDCKR	SC70	DCK	5	3000	180.0	180.0	18.0
LMV321IDCKR	SC70	DCK	5	3000	205.0	200.0	33.0
LMV321IDCKT	SC70	DCK	5	250	205.0	200.0	33.0
LMV321IDCKT	SC70	DCK	5	250	180.0	180.0	18.0
LMV324IDR	SOIC	D	14	2500	333.2	345.9	28.6
LMV324IDR	SOIC	D	14	2500	364.0	364.0	27.0

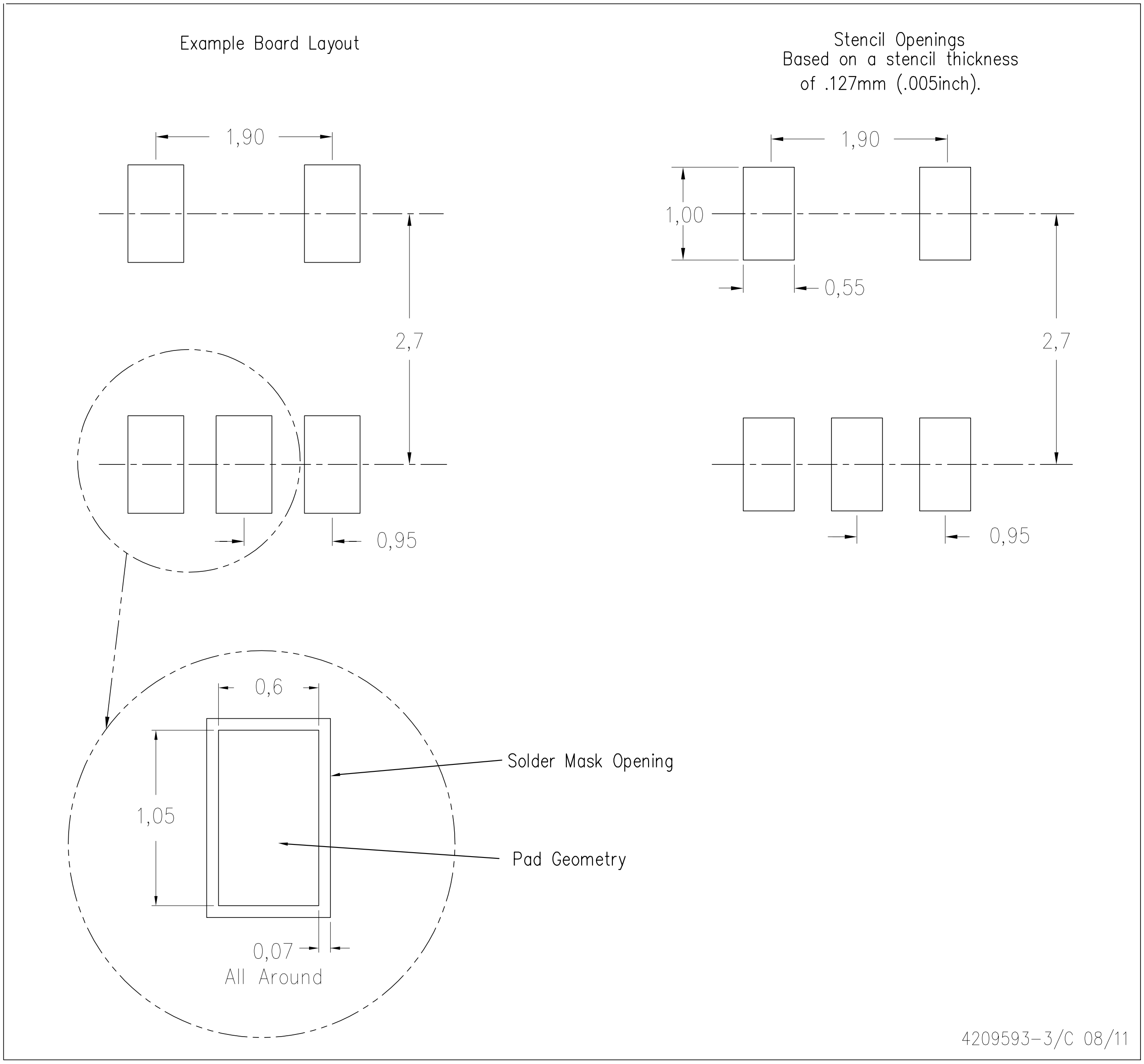
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
LMV324IDRG4	SOIC	D	14	2500	333.2	345.9	28.6
LMV324IPWR	TSSOP	PW	14	2000	364.0	364.0	27.0
LMV324IPWRG4	TSSOP	PW	14	2000	367.0	367.0	35.0
LMV324QDR	SOIC	D	14	2500	367.0	367.0	38.0
LMV324QPWR	TSSOP	PW	14	2000	367.0	367.0	35.0
LMV358IDDUR	VSSOP	DDU	8	3000	202.0	201.0	28.0
LMV358IDGKR	VSSOP	DGK	8	2500	358.0	335.0	35.0
LMV358IDR	SOIC	D	8	2500	340.5	338.1	20.6
LMV358IDR	SOIC	D	8	2500	367.0	367.0	35.0
LMV358IDR	SOIC	D	8	2500	364.0	364.0	27.0
LMV358IDRG4	SOIC	D	8	2500	340.5	338.1	20.6
LMV358IPWR	TSSOP	PW	8	2000	364.0	364.0	27.0
LMV358QDDUR	VSSOP	DDU	8	3000	202.0	201.0	28.0
LMV358QDGKR	VSSOP	DGK	8	2500	358.0	335.0	35.0
LMV358QDR	SOIC	D	8	2500	340.5	338.1	20.6

DBV (R-PDSO-G5) PLASTIC SMALL-OUTLINE PACKAGE



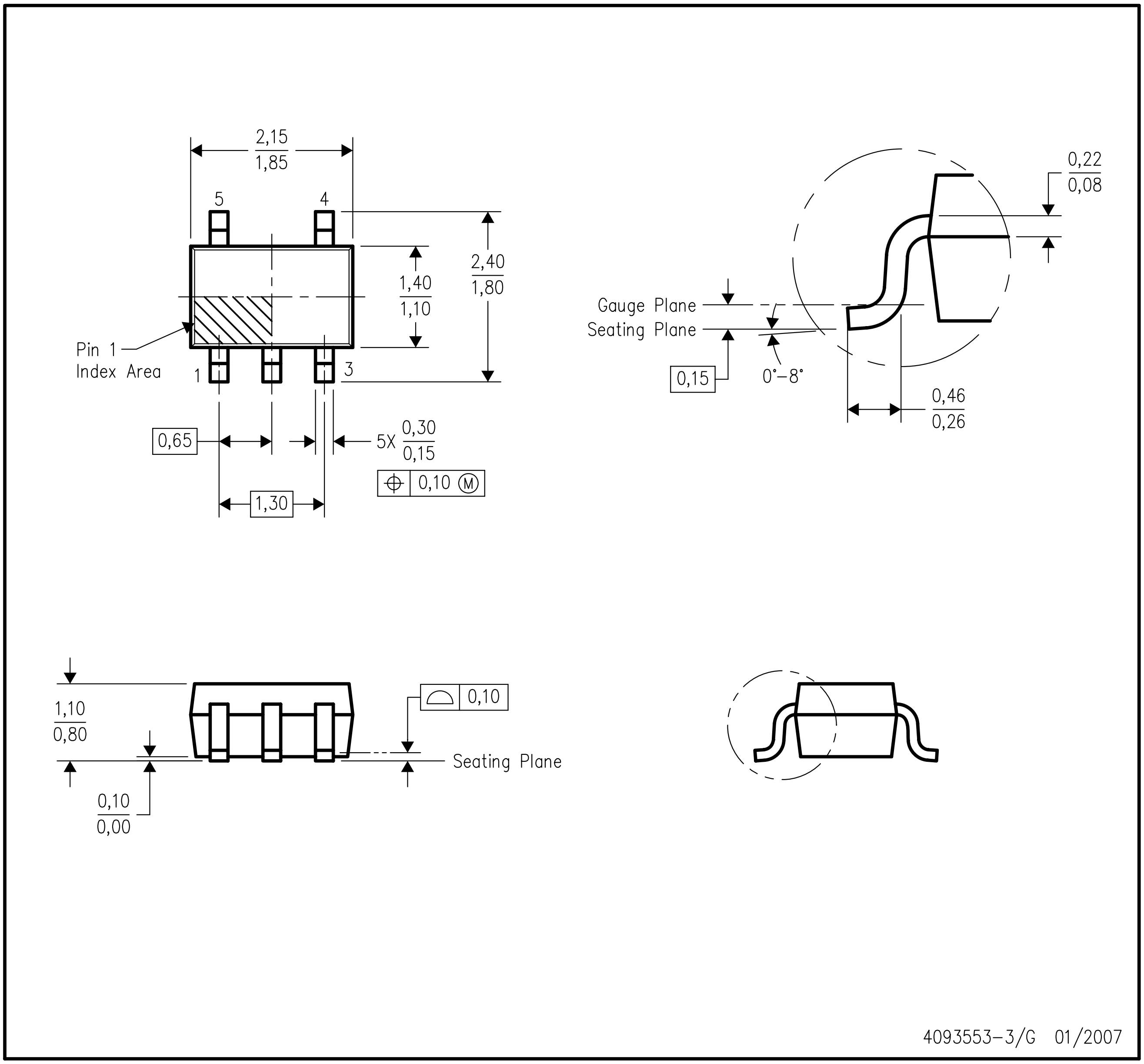
NOTES: A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.15 per side.
D. Falls within JEDEC MO-178 Variation AA.

DBV (R–PDSO–G5) PLASTIC SMALL OUTLINE



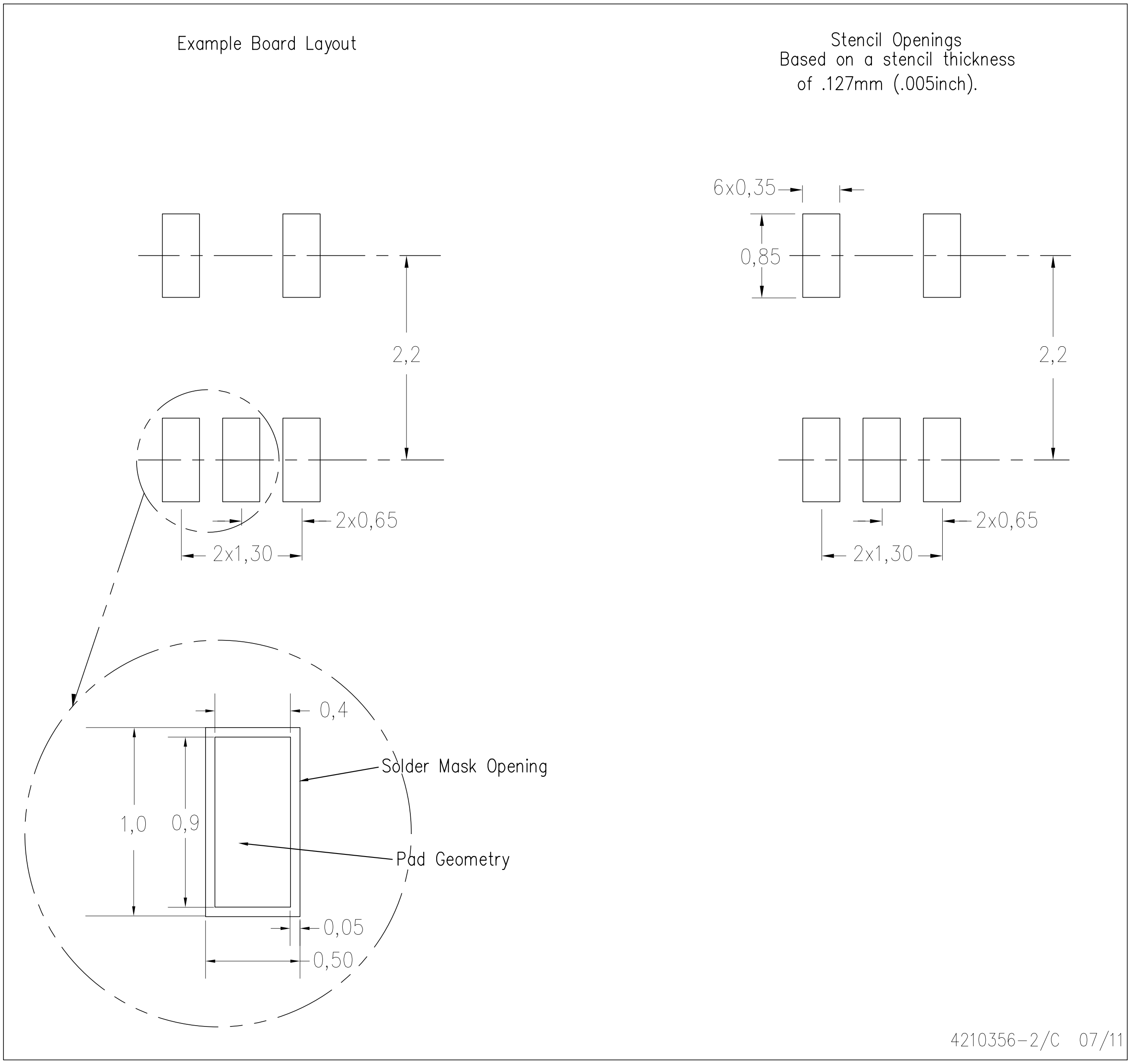
NOTES:
A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Customers should place a note on the circuit board fabrication drawing not to alter the center solder mask defined pad.
D. Publication IPC–7351 is recommended for alternate designs.
E. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Example stencil design based on a 50% volumetric metal load solder paste. Refer to IPC–7525 for other stencil recommendations.

DCK (R-PDSO-G5) PLASTIC SMALL-OUTLINE PACKAGE



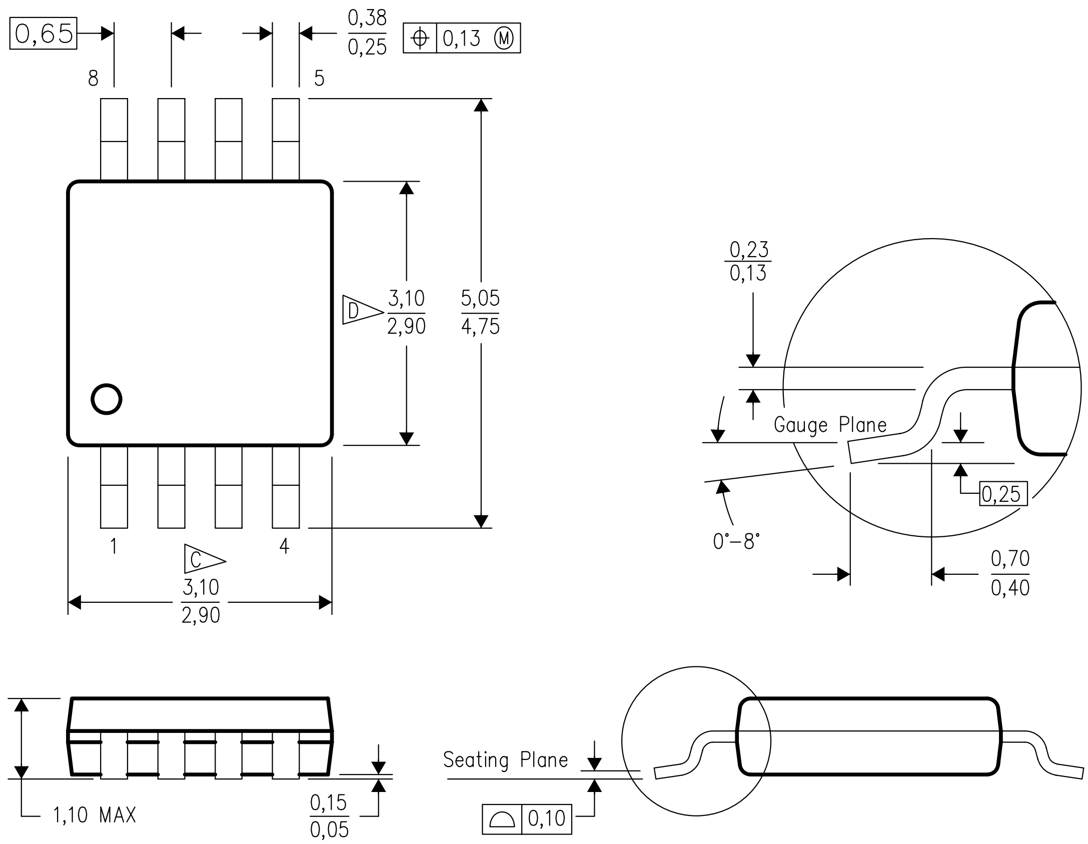
NOTES:
- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.15 per side.
- D. Falls within JEDEC MO-203 variation AA.

DCK (R–PDSO–G5) PLASTIC SMALL OUTLINE



NOTES:
A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Customers should place a note on the circuit board fabrication drawing not to alter the center solder mask defined pad.
D. Publication IPC–7351 is recommended for alternate designs.
E. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Example stencil design based on a 50% volumetric metal load solder paste. Refer to IPC–7525 for other stencil recommendations.

DGK (S-PDSO-G8) PLASTIC SMALL-OUTLINE PACKAGE



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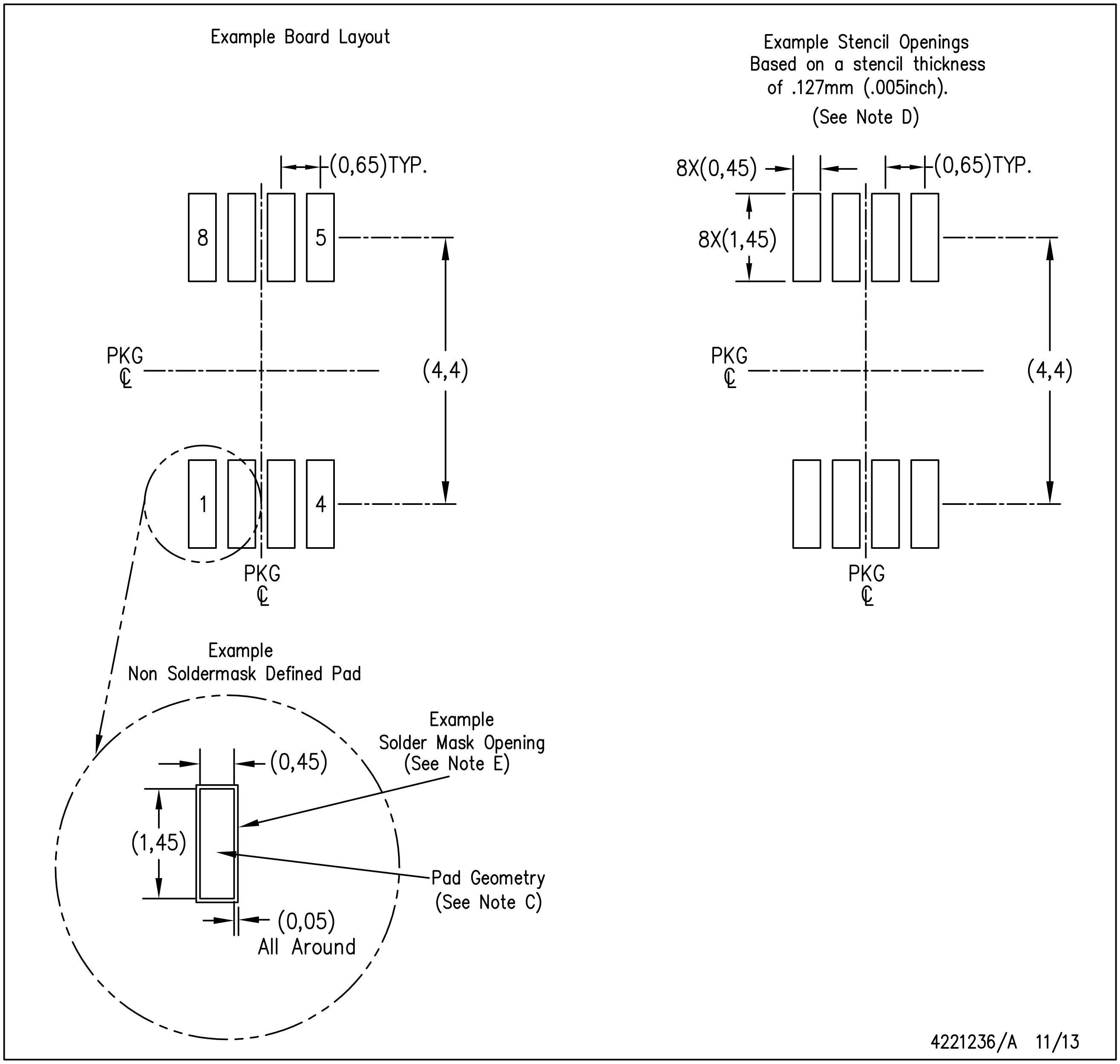
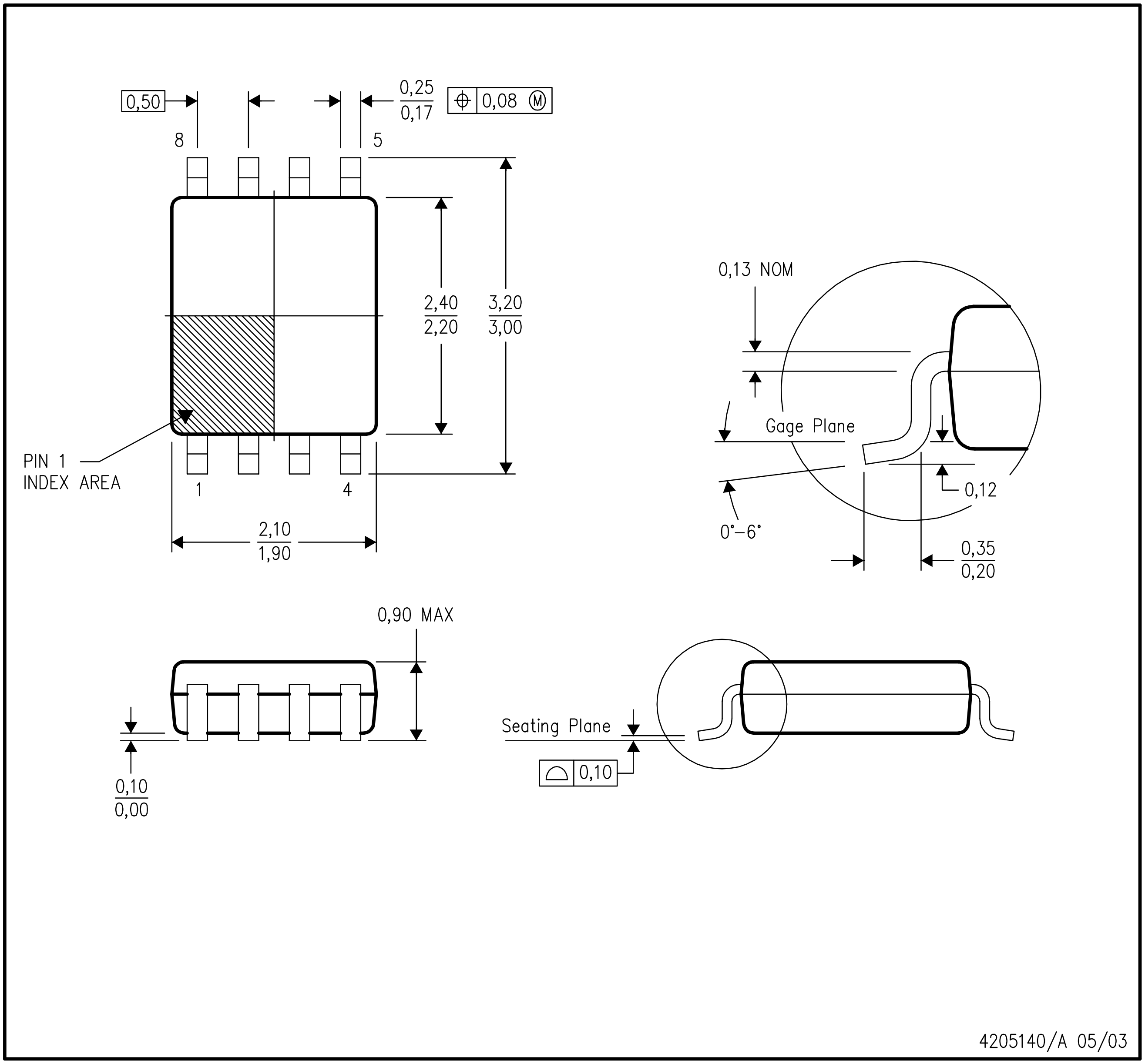
NOTES:
A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 per end.
D. Body width does not include interlead flash. Interlead flash shall not exceed 0.50 per side.
E. Falls within JEDEC MO-187 variation AA, except interlead flash.

DGK (S–PDSO–G8) PLASTIC SMALL OUTLINE PACKAGE



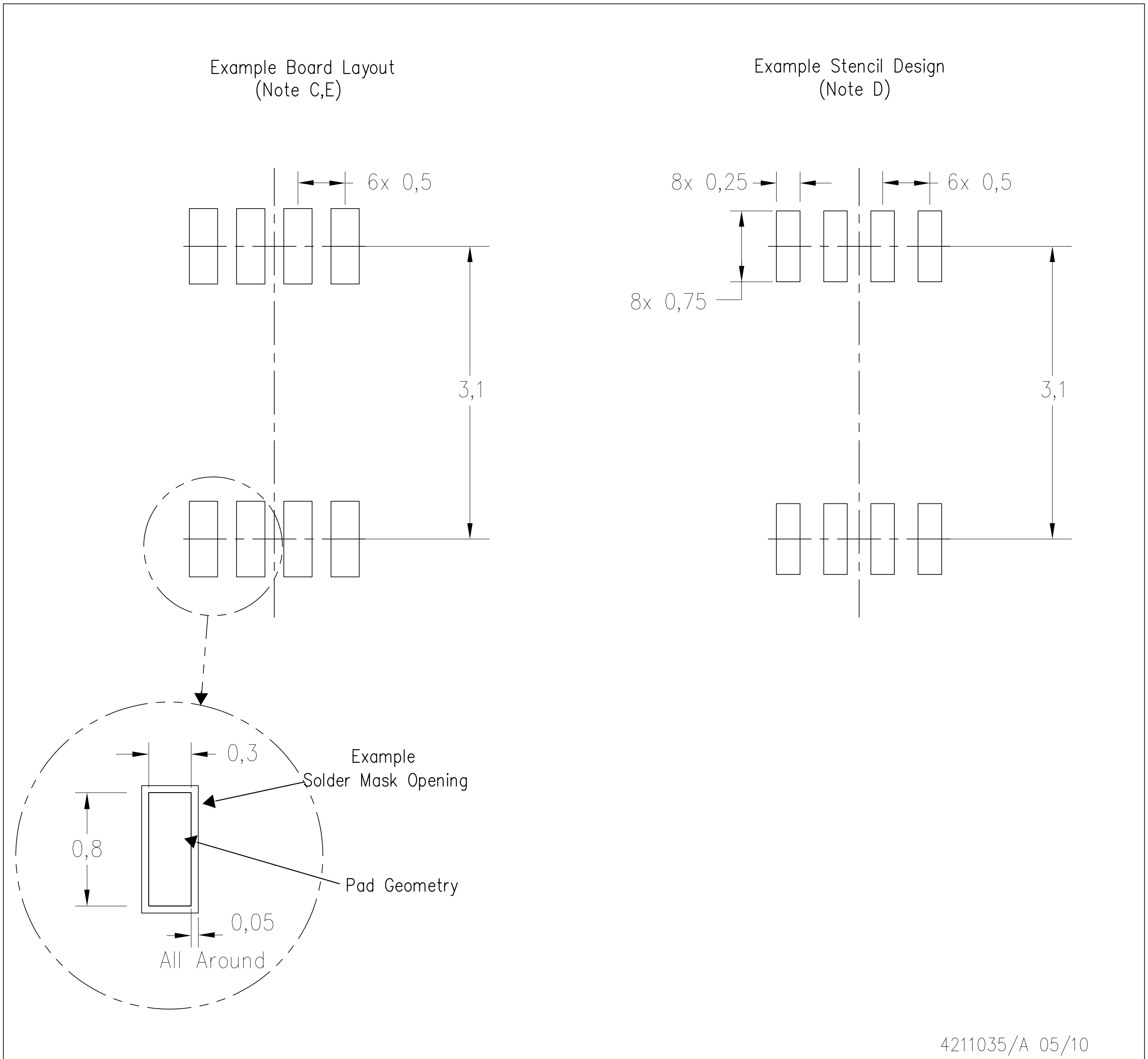
NOTES:
- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Publication IPC–7351 is recommended for alternate designs.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC–7525 for other stencil recommendations.
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

DDU (R-PDSO-G8) PLASTIC SMALL-OUTLINE PACKAGE



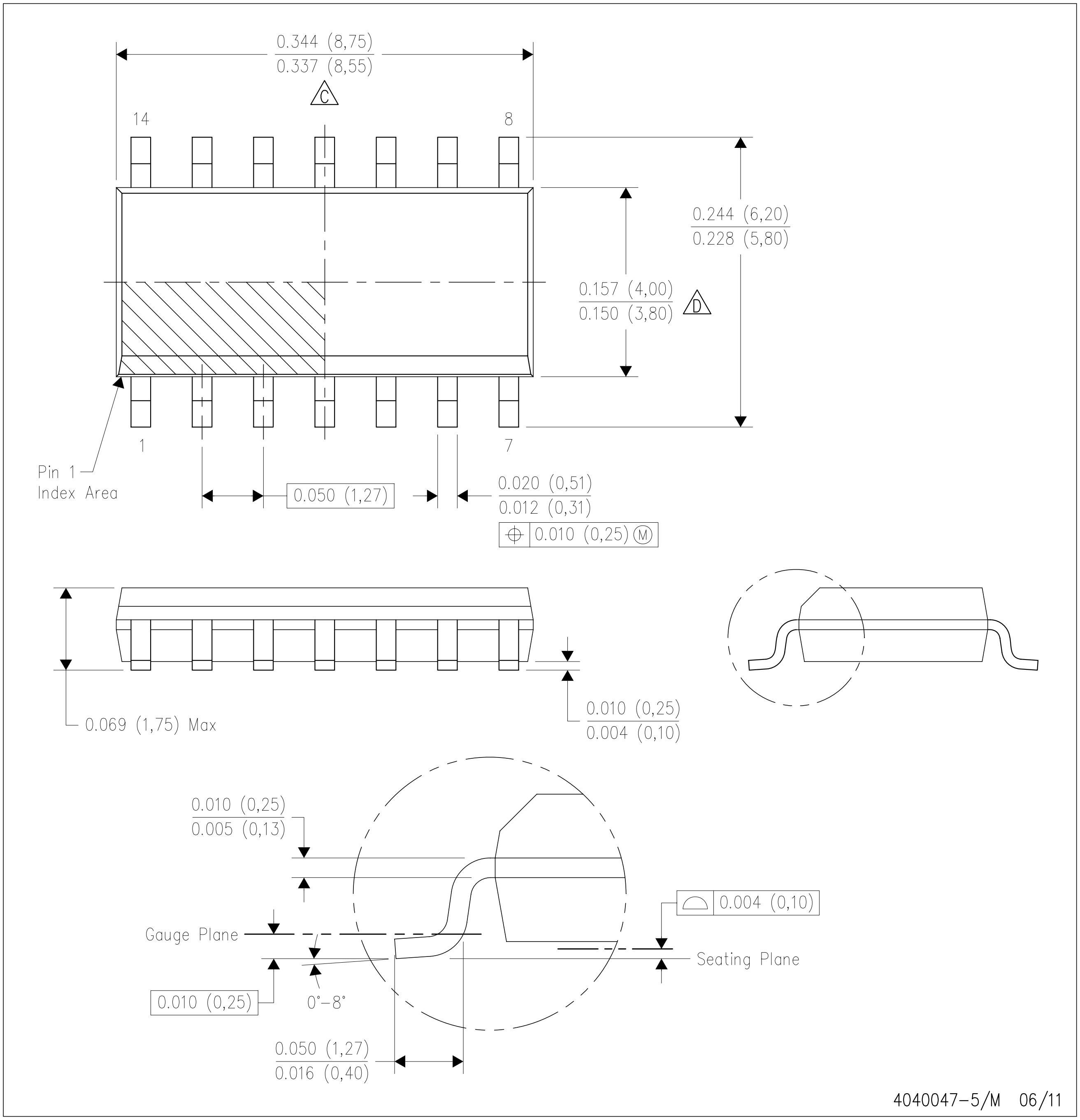
NOTES:
- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Body dimensions do not include mold flash or protrusion.
- D. Falls within JEDEC MO–187 variation CA.

DDU (S-PDSO-G8) PLASTIC SMALL OUTLINE PACKAGE (DIE UP)



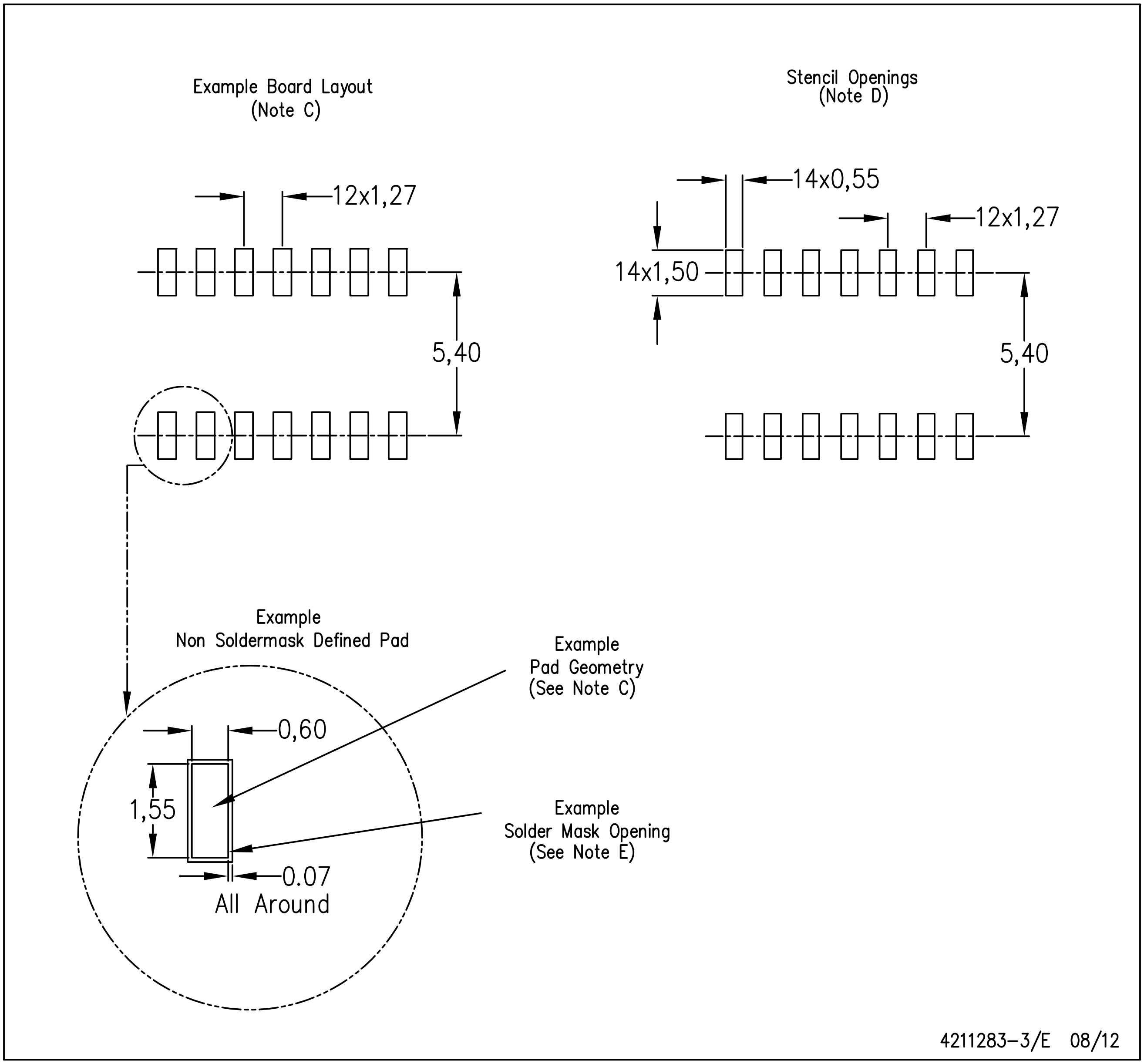
NOTES: A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Publication IPC-7351 is recommended for alternate designs.
D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525.
E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

D (R–PDSO–G14) PLASTIC SMALL OUTLINE



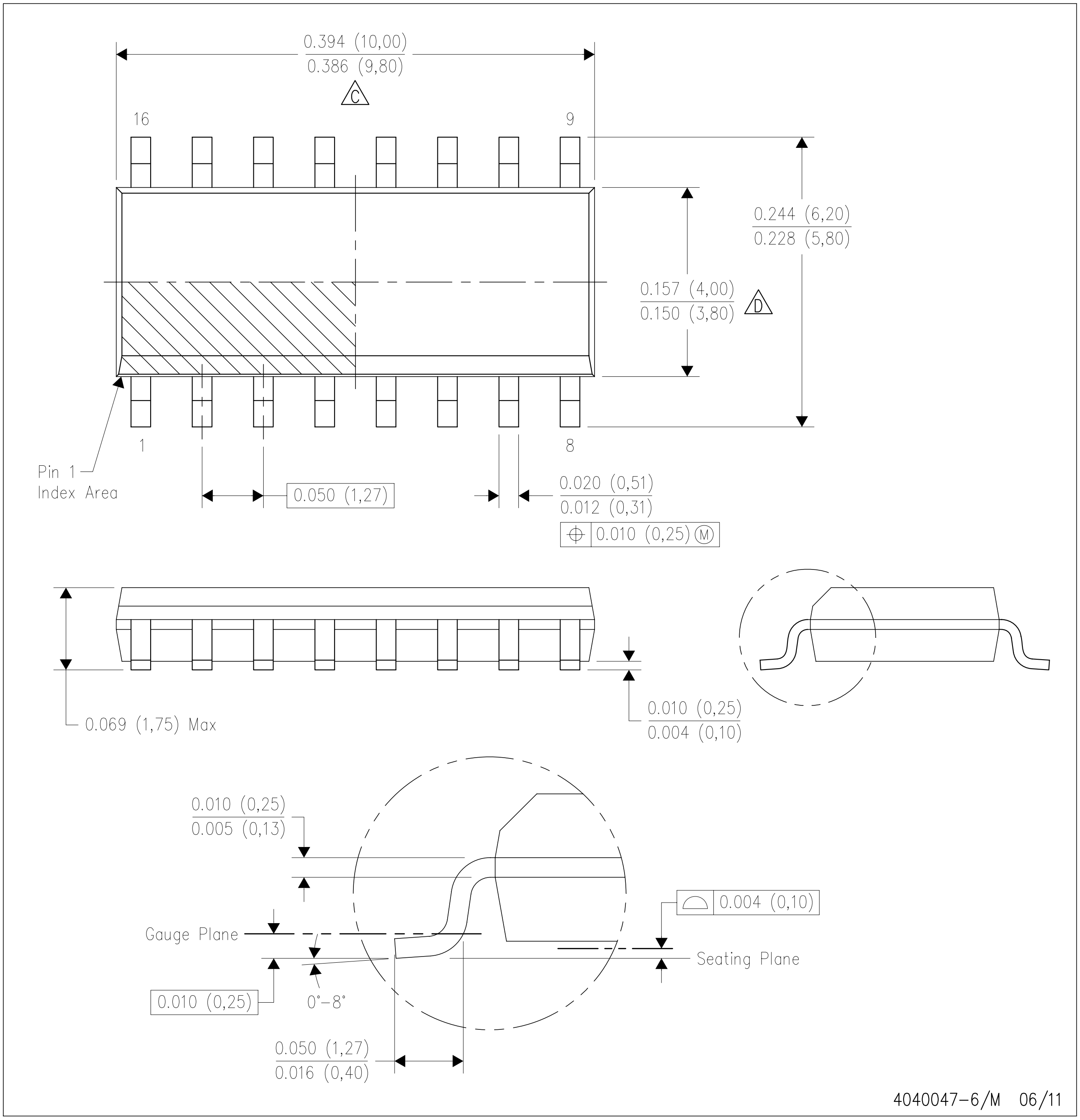
NOTES:
A. All linear dimensions are in inches (millimeters).
B. This drawing is subject to change without notice.
C. Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
D. Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
E. Reference JEDEC MS-012 variation AB.

D (R-PDSO-G14) PLASTIC SMALL OUTLINE



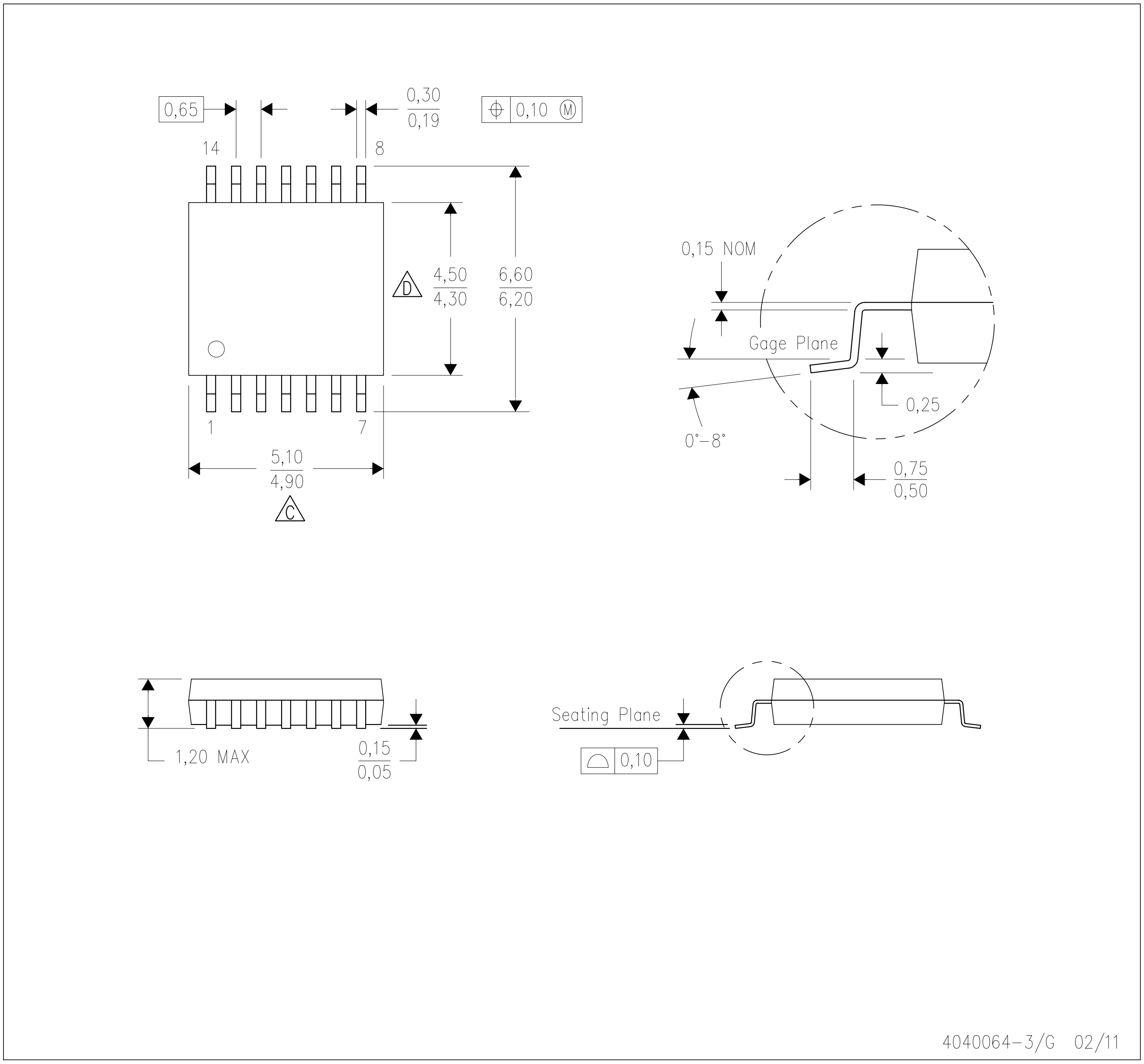
NOTES:
A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Publication IPC-7351 is recommended for alternate designs.
D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

D (R-PDSO-G16) PLASTIC SMALL OUTLINE



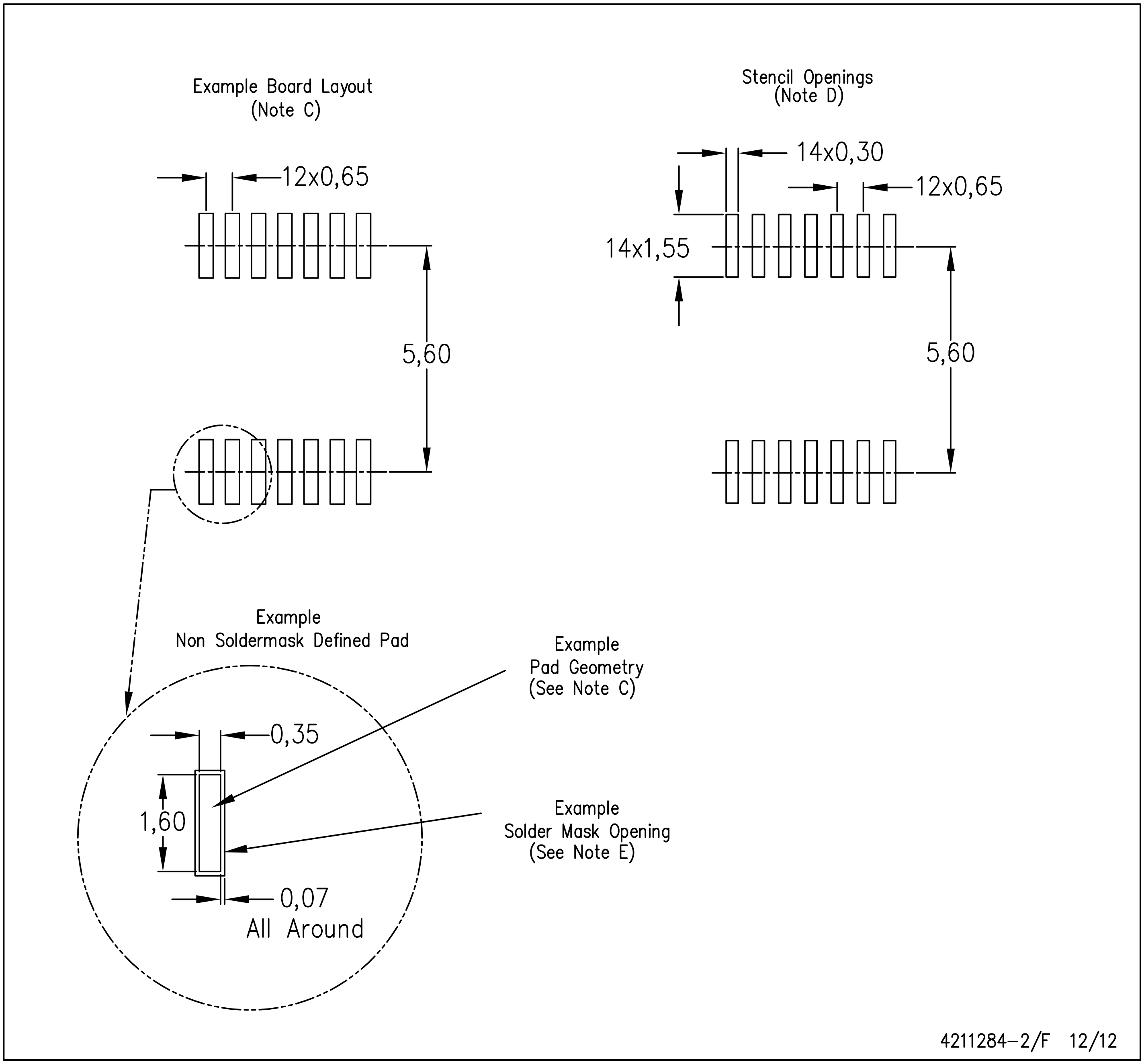
NOTES:
- A. All linear dimensions are in inches (millimeters).
- B. This drawing is subject to change without notice.
- C. Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
- D. Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
- E. Reference JEDEC MS-012 variation AC.

PW (R–PDSO–G14)   PLASTIC SMALL OUTLINE



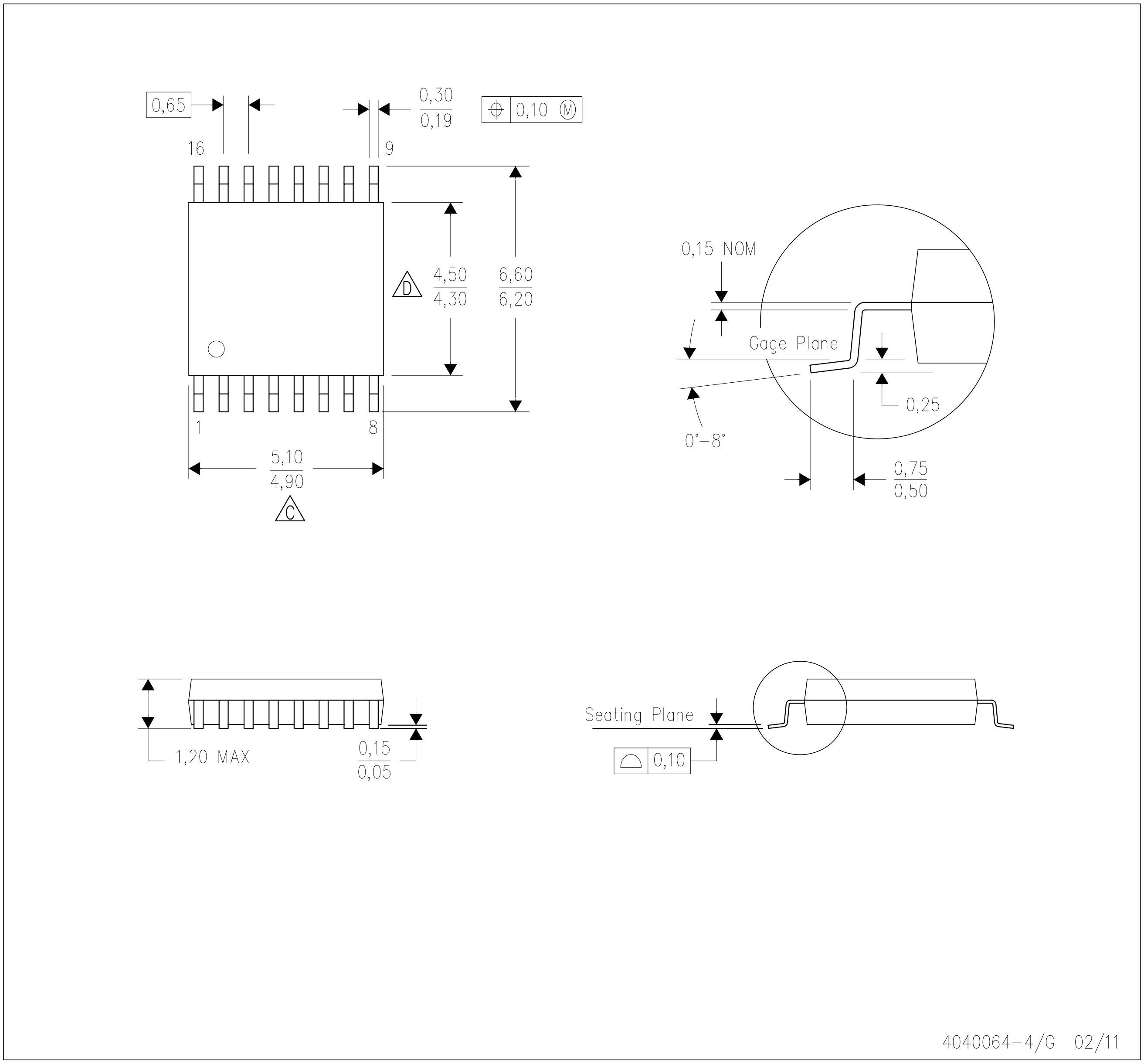
NOTES:
A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M–1994.
B. This drawing is subject to change without notice.
C. Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0,15 each side.
D. Body width does not include interlead flash. Interlead flash shall not exceed 0,25 each side.
E. Falls within JEDEC MO–153

PW (R-PDSO-G14) PLASTIC SMALL OUTLINE



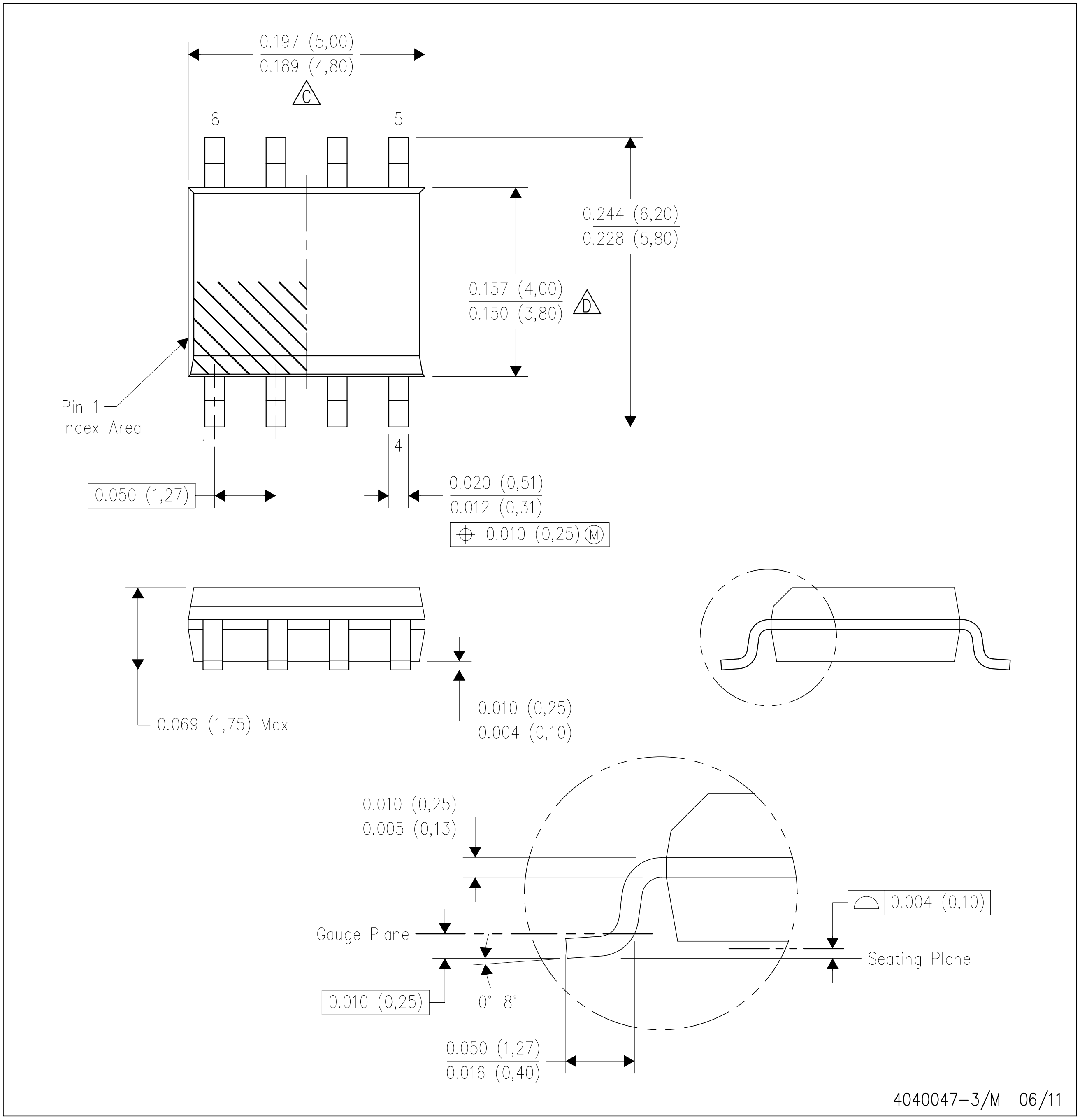
NOTES:
A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Publication IPC-7351 is recommended for alternate designs.
D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

PW (R–PDSO–G16) PLASTIC SMALL OUTLINE



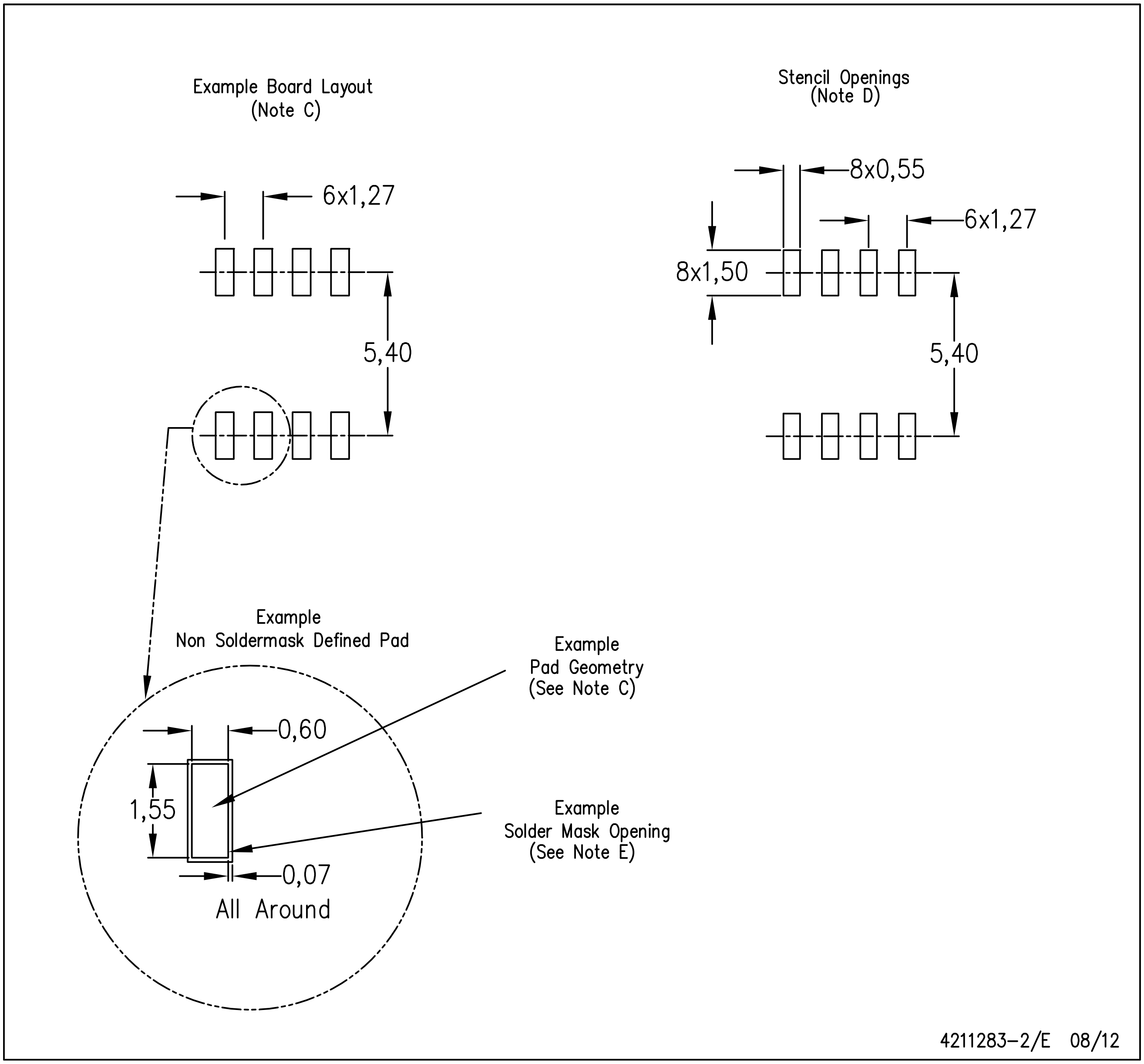
NOTES:
- A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M–1994.
- B. This drawing is subject to change without notice.
- C. Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0,15 each side.
- D. Body width does not include interlead flash. Interlead flash shall not exceed 0,25 each side.
- E. Falls within JEDEC MO–153

D (R-PDSO-G8) PLASTIC SMALL OUTLINE



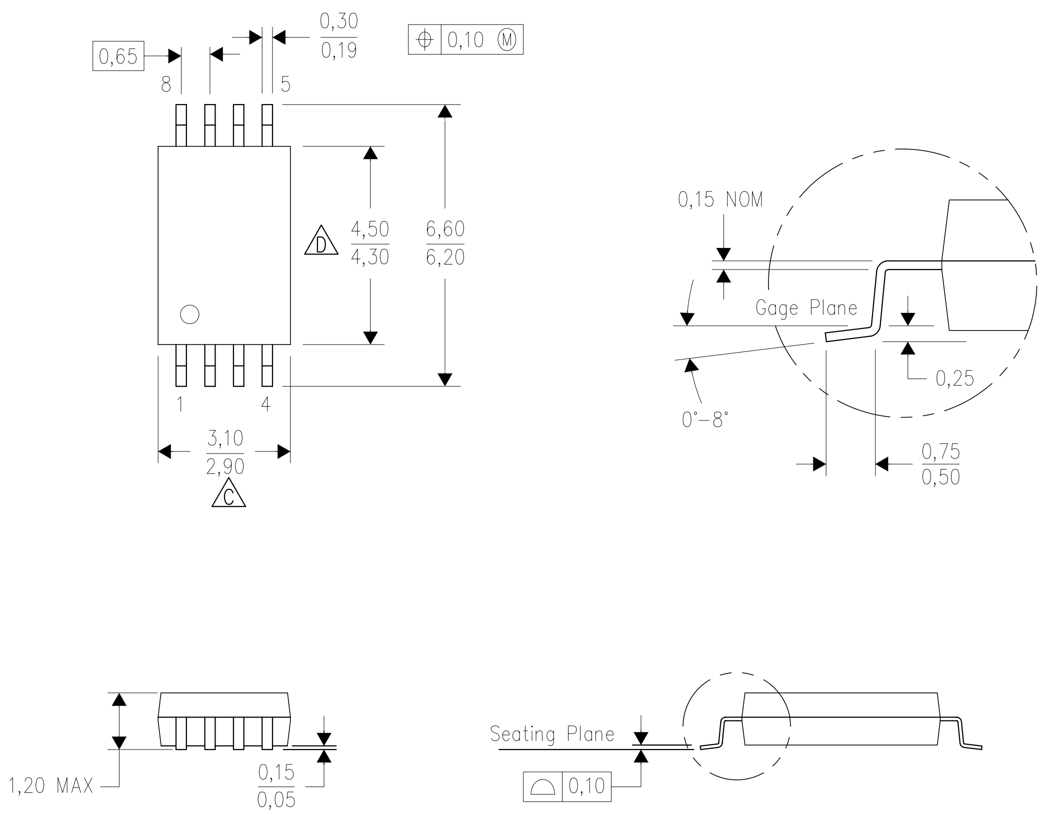
NOTES:
A. All linear dimensions are in inches (millimeters).
B. This drawing is subject to change without notice.
C. Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.006 (0,15) each side.
D. Body width does not include interlead flash. Interlead flash shall not exceed 0.017 (0,43) each side.
E. Reference JEDEC MS-012 variation AA.

D (R-PDSO-G8) PLASTIC SMALL OUTLINE



NOTES:
A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Publication IPC-7351 is recommended for alternate designs.
D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

PW (R-PDSO-G8) PLASTIC SMALL OUTLINE



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NOTES:
- A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M–1994.
- B. This drawing is subject to change without notice.
- C. Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0,15 each side.
- D. Body width does not include interlead flash. Interlead flash shall not exceed 0,25 each side.
- E. Falls within JEDEC MO–153

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